

ISOW774x 低放射、低ノイズ DC/DC コンバータ内蔵、クワッド・チャネル・デジタル・アイソレータ

1 特長

- 100Mbps のデータ・レート
- 低放射、低ノイズ DC/DC コンバータを内蔵
 - CISPR 32 および EN 55032 Class B の放射要件を満たし、2 層基板で 5dB を上回るマージンを確保するように最適化
 - 25MHz 動作の低周波数パワー・コンバータにより低ノイズ特性を実現
 - 低い出力リップル: 24mV
- 高効率出力電力
 - 最大負荷時の効率: 46%
 - 最大 0.55W の出力電力
 - V_{ISOOUT} 精度: 5%
 - 5V から 5V へ: 最大利用可能負荷電流 = 110mA
 - 5V から 3.3V へ: 最大利用可能負荷電流 = 140mA
 - 3.3V から 3.3V へ: 最大利用可能負荷電流 = 60mA
- チャネル・アイソレータ用とパワー・コンバータ用に独立した電源
 - ロジック電源 (V_{IO}): 1.71V ~ 5.5V
 - パワー・コンバータ電圧 (V_{DD}): 3V ~ 5.5V
- 堅牢な電磁両立性 (EMC)
 - システム・レベルでの ESD、EFT、サージ耐性
 - 絶縁バリアの両側で $\pm 8kV$ の IEC 61000-4-2 接触放電保護
- 強化絶縁型と基本絶縁型のオプション
- 高 CMTI: 100kV/ μs (標準値)
- 安全関連認証:
 - DIN VDE V 0884-11:2017-01 準拠の VDE 強化絶縁および基本絶縁
 - UL 1577 部品認定プログラム
 - IEC 62368-1、IEC 61010-1、IEC 60601-1、GB 4943.1-2011 認証
 - ISOW774xB デバイスを計画中
- 拡張温度範囲: $-40^{\circ}C \sim +125^{\circ}C$
- 20 ピンのワイド・ボディ SOIC パッケージ

2 アプリケーション

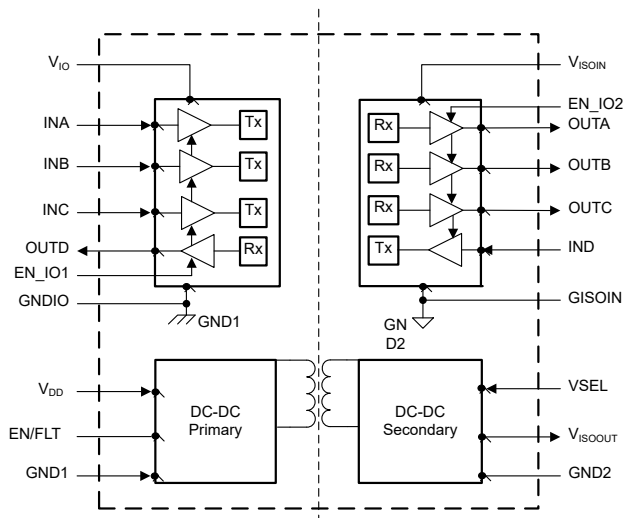
- ファクトリ・オートメーション
- モーター制御
- グリッド・インフラストラクチャ
- 医療用機器
- 試験および測定機器

3 概要

ISOW77xx デバイス・ファミリは、低放射で高効率の電力コンバータを内蔵した、ガルバニック絶縁されたクワッド・チャネル・デジタル・アイソレータです。内蔵の DC-DC コンバータにより、最大 550mW の絶縁電力を供給できるため、スペースに制約のある絶縁設計において個別の絶縁電源が不要です。

デバイス情報

機能	ISOW774x ISOW774xF	ISOW774xB ISOW774xFB
保護レベル	強化	基本
サージ・テスト電圧	10kV _{PK}	7.8kV _{PK}
定格絶縁電圧	5000V _{RMS}	5000V _{RMS}
動作電圧	、1000V _{RMS} / 1500V _{PK}	、1000V _{RMS} / 1500V _{PK}
パッケージ	DFM (20)	DFM (20)
本体サイズ (公称)	12.83mm × 7.5mm	12.83mm × 7.5mm



ISOW7741 概略回路図



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision B (January 2022) to Revision C (April 2022)	Page
• Added ISOW7740, ISOW7742, ISOW7743 and ISOW7744 Typical Characteristics.....	32

Changes from Revision A (October 2021) to Revision B (January 2022)	Page
• ISOW7740、ISOW7742、ISOW7743、ISOW7744 をデータシートに追加。.....	1

Changes from Revision * (September 2021) to Revision A (October 2021)	Page
• デバイスのステータスを「量産データ」に更新.....	1

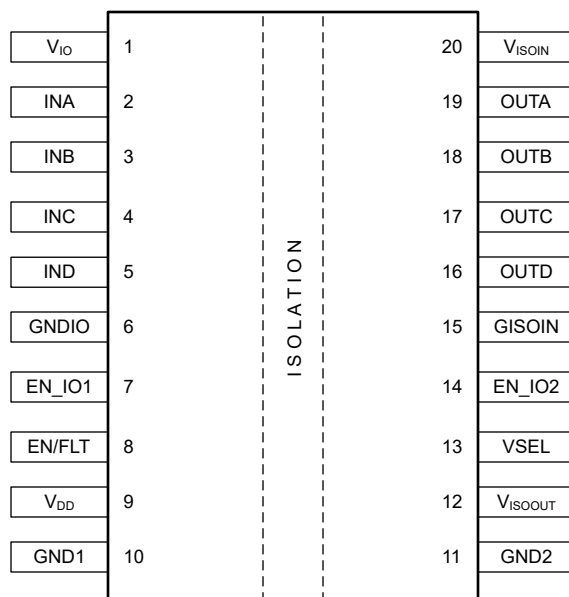
5 概要 (続き)

このパワー・コンバータは効率が高いため、 -40°C ~ $+125^{\circ}\text{C}$ の広い周囲温度範囲で動作します。このデバイスは、放射性能が改善されているのでボード設計を簡素化でき、フェライト・ビーズを取り付けてさらに放射を減衰させることができます。ISOW774x は、突入電流を制限するソフトスタート、過電圧および低電圧誤動作防止、EN/FLT ピンでのフォルト検出、過負荷および短絡保護、サーマル・シャットダウンなど、保護機能の強化を念頭に置いて設計されています。

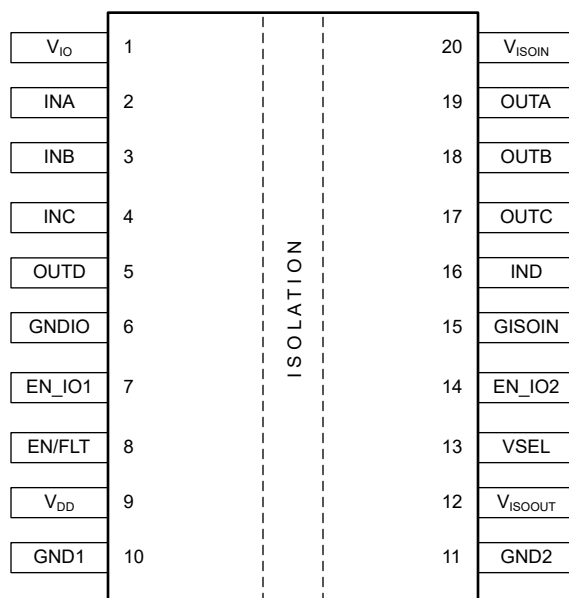
ISOW77xx デバイス・ファミリは、CMOS または LVCMOS デジタル I/O を絶縁するとともに、高い電磁耐性を備えています。信号絶縁チャネルでは、ロジック入力および出力バッファが二酸化ケイ素 (SiO_2) の二重容量性絶縁バリアによって分離されています。また電力絶縁では、薄膜ポリマーを絶縁素材としたオンチップの変圧器を使用しています。4 チャネル ISOW77xx は 5 つの構成が注文可能で、型番の末尾の数字は逆方向チャネルの数を示しています。たとえば、ISOW7740 には 4 つの順方向チャネルと 0 の逆方向チャネルがあり、ISOW7743 には 1 つの順方向チャネルと 3 つの逆方向チャネルがあります。入力信号が消失した場合のデフォルト出力は、接尾辞 F の付いていない ISOW77xx デバイスでは HIGH となり、接尾辞 F の付いている ISOW77xx デバイスでは LOW となります。ISOW774x は、 V_{IO} と V_{DD} を PCB 上で接続することにより、3V~5.5V の単一電源電圧で動作できます。より低いロジック・レベルが必要とされる場合、これらのデバイスは、3V~5.5V のパワー・コンバータ電源電圧 (V_{DD}) とは別に、1.71V~5.5V のロジック電源 (V_{IO}) に対応可能です。 V_{ISOIN} と V_{ISOOUT} は、基板上でフェライト・ビーズを使用して両者の間を接続するか、または LDO により電源を供給する必要があります。

これらのデバイスを使用すれば、UART、SPI、RS-485、RS-232、CAN などのデータバスや他の回路のノイズ電流がローカル・グラウンドに混入して敏感な回路に干渉や損傷を与えることを防止できます。革新的なチップ設計およびレイアウト技法により、このデバイスは電磁両立性が大幅に強化されているため、システム・レベルの ESD、EFT、サージ、および放射のコンプライアンスを容易に達成できます。このデバイスは、20 ピンの SOIC ワイド・ボディ (SOIC-WB) DFM パッケージで供給されます。

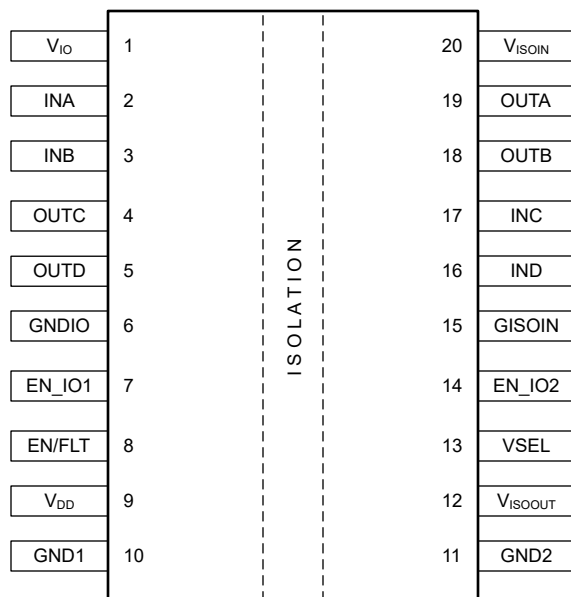
6 Pin Configuration and Functions



6-1. ISOW7740 DFM Package 20-Pin SOIC-WB Top View



6-2. ISOW7741 DFM Package 20-Pin SOIC-WB Top View



6-3. ISOW7742 DFM Package 20-Pin SOIC-WB Top View

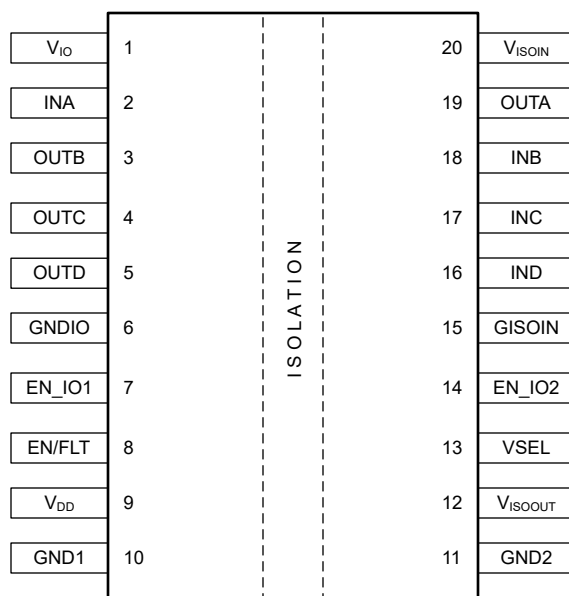


FIG 6-4. ISOW7743 DFM Package 20-Pin SOIC-WB Top View

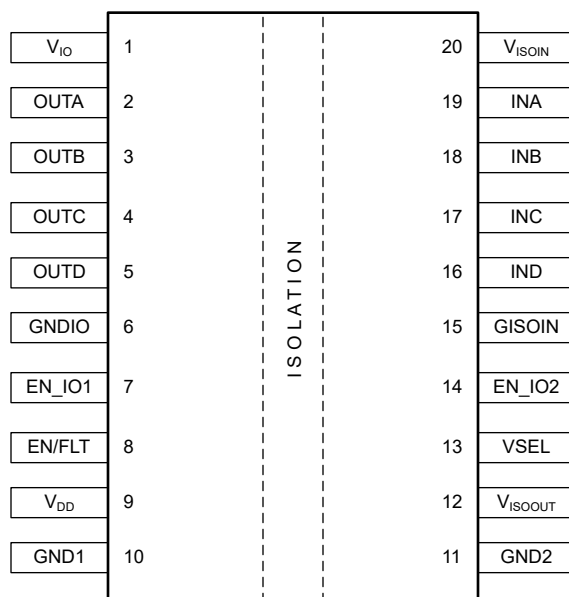


FIG 6-5. ISOW7744 DFM Package 20-Pin SOIC-WB Top View

NAME	PIN NO.					I/O	DESCRIPTION
	ISOW7740	ISOW7741	ISOW7742	ISOW7743	ISOW7744		
GNDIO	6	6	6	6	6	—	Ground connection for V_{IO} . GND1 and GNDIO needs to be shorted on board.
GND1	10	10	10	10	10	—	Ground connection for V_{DD} . GND1 and GNDIO needs to be shorted on board.
GND2	11	11	11	11	11	—	Ground connection for V_{ISOOUT} . GND2 and GISOIN pins can be shorted on board or connected through a ferrite bead. See the Layout Section for more information.
GISOIN	15	15	15	15	15	—	Ground connection for V_{ISOIN} . GND2 and GISOIN pins can be shorted on board or connected through a ferrite bead. See the Layout Section for more information.
INA	2	2	2	2	19	I	Input channel A

PIN						I/O	DESCRIPTION
NAME	NO.						
	ISOW7740	ISOW7741	ISOW7742	ISOW7743	ISOW7744		
INB	3	3	3	18	18	I	Input channel B
INC	4	4	17	17	17	I	Input channel C
IND	5	16	16	16	16	I	Input channel D
OUTA	19	19	19	19	2	O	Output channel A
OUTB	18	18	18	3	3	O	Output channel B
OUTC	17	17	4	4	4	O	Output channel C
OUTD	16	5	5	5	5	O	Output channel D
EN_IO1	7	7	7	7	7	I	Output Enable 1: When EN_IO1 is high or open then the channel output pins on side 1 are enabled. When EN_IO1 is low then the channel output pins on side 1 are in a high impedance state and the transmitter of the channel input pins on side 1 are disabled.
EN_IO2	14	14	14	14	14	I	Output Enable 2: When EN_IO2 is high or open then the channel output pins on side 2 are enabled. When EN_IO2 is low then the channel output pins on side 2 are in a high impedance state and the transmitter of the channel input pins on side 2 are disabled.
EN/FLT	8	8	8	8	8	I/O	Multi-function power converter enable input pin or fault output pin. Can only be used as either an input pin or an output pin. Power converter enable input pin: enables and disables the integrated DC-DC power converter. Connect directly to microcontroller or through a series current limiting resistor to use as an enable input pin. DC-DC power converted is enabled when EN/FLT is high to the V _{IO} voltage level and disabled when low at GND1 voltage level. Fault output pin: Alert signal if power converter is not operating properly. This pin is active low. Connect to microcontroller through a 5 kΩ or greater pull-up resistor in order to use as a fault outpin pin. See セクション 9.3.3 for more information
VSEL	13	13	13	13	13	I	V _{ISOOUT} selection pin. V _{ISOOUT} = 5 V when VSEL shorted to V _{ISOOUT} . V _{ISOOUT} = 3.3 V, when VSEL shorted to GND2. For more information see the Device Functional Modes .
V _{IO}	1	1	1	1	1	—	Side 1 logic supply.
V _{BD}	9	9	9	9	9	—	Side 1 DC-DC converter power supply.
V _{ISOIN}	20	20	20	20	20	—	Side 2 supply voltage for isolation channels. V _{ISOIN} and V _{ISOOUT} pins can be shorted on board or connected through a ferrite bead. See Application and Implementation for more information.
V _{ISOOUT}	12	12	12	12	12	—	Isolated power converter output voltage. V _{ISOIN} and V _{ISOOUT} pins can be shorted on board or connected through a ferrite bead. See Application and Implementation for more information.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

		MIN	MAX	UNIT
V _{DD}	Power converter supply voltage	−0.5	6	V
V _{ISOIN}	Isolated supply voltage, input supply for secondary side isolation channels	−0.5	6	V
V _{ISOOUT}	Isolated supply voltage, Power converter output V _{SEL} shorted to GND2	−0.5	4	V
V _{ISOOUT}	Isolated supply voltage, Power converter output V _{SEL} shorted to V _{ISOOUT}	−0.5	6	V
V _{IO}	Primary side logic supply voltage	−0.5	6	V
V	Voltage at INx, OUTx, EN_IOx ⁽³⁾	−0.5	V _{SI} + 0.5	V
	Voltage at EN/FLT	−0.5	V _{SI} + 0.5	V
	Voltage at VSEL	−0.5	V _{ISOOUT} + 0.5	V
I _O	Maximum output current through data channels	−15	15	mA
T _J	Junction temperature	−40	150	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) V_{DD}, V_{ISOIN}, V_{ISOOUT}, and V_{IO} are with respect to the local ground pin (GND1 or GND2). All voltage values except differential I/O bus voltages are peak voltage values.
- (3) V_{SI} = input side supply; Cannot exceed 6 V.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±3000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level C6	±1500	
		Contact discharge per IEC 61000-4-2 ⁽²⁾ Isolation barrier withstand test	±8000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.
- (2) IEC ESD strike is applied across the barrier with all pins on each side tied together creating a two-terminal device.

7.3 Recommended Operating Conditions

Over recommended operating conditions, typical values are at $V_{DD} = V_{IO} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$, GND1 = GNDIO, GND2 = GISOIN (unless otherwise noted)

			MIN	NOM	MAX	UNIT
Power Converter						
V_{DD}	Power converter supply voltage	3.3 V operation	2.97	3.3	3.63	V
		5 V operation	4.5	5	5.5	V
$V_{DD(UVLO+)}$	Positive threshold when power converter supply is rising	Positive threshold when power converter supply is rising		2.7	2.95	V
$V_{DD(UVLO-)}$	Positive threshold when power converter supply is falling	Positive threshold when power converter supply is falling	2.40	2.55		V
$V_{DD(HYS)}$	Power converter supply voltage hysteresis	Power converter supply voltage hysteresis	0.15			V
Channel Isolation						
V_{IO}, V_{ISOIN} ⁽³⁾	Channel logic supply voltage	1.8 V operation	1.71		1.89	V
		2.5 V, 3.3 V, and 5 V operation	2.25		5.5	V
$V_{IO(UVLO+)}$	Rising threshold of logic supply voltage			1.55	1.7	V
$V_{IO(UVLO-)}$	Falling threshold of logic supply voltage		1.0	1.41		V
$V_{IO(HYS)}$	Logic supply voltage hysteresis		75			mV
I_{OH}	High level output current ⁽¹⁾	$V_{ISOIN} = 5\text{ V}$	–4			mA
		$V_{ISOIN} = 3.3\text{ V}$	–2			mA
		$V_{ISOIN} = 2.5\text{ V}$	–1			mA
		$V_{ISOIN} = 1.8\text{ V}$	–1			mA
I_{OL}	Low level output current ⁽¹⁾	$V_{ISOIN} = 5\text{ V}$			4	mA
		$V_{ISOIN} = 3.3\text{ V}$			2	mA
		$V_{ISOIN} = 2.5\text{ V}$			1	mA
		$V_{ISOIN} = 1.8\text{ V}$			1	mA
V_{IH}	High-level input voltage ⁽²⁾		$0.7 \times V_{SI}$		V_{SI}	V
V_{IL}	Low-level input voltage		0		$0.3 \times V_{SI}$	V
DR	Data rate				100	Mbps
t_{PWRUP}	Channel isolator ready after power up or EN/FLT high	$V_{ISOIN} > V_{IO(UVLO+)}$		5		ms
T_A	Ambient temperature		–40		125	°C

(1) This current is for data output channel.

(2) V_{SI} = input side supply; V_{SO} = output side supply

(3) The channel outputs are in undetermined state when $1.89\text{ V} < V_{SI} < 2.25\text{ V}$ and $1.05\text{ V} < V_{SI} < 1.71\text{ V}$

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		ISOW774x	UNIT
		DFM (SOIC)	
		20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	68.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	24.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	53.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	17.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	50.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

7.5 Power Ratings

$V_{DD} = V_{IO} = 5.5\text{ V}$, $I_{ISO} = 110\text{ mA}$, $T_J = 150^\circ\text{C}$, $T_A \leq 80^\circ\text{C}$, $C_L = 15\text{ pF}$, input a 50-MHz 50% duty-cycle square wave

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation (both sides)	$V_{DD} = 5.5\text{ V}$, $V_{IO} = 5.5\text{ V}$, $V_{ISOOUT} = V_{ISOIN}$, $I_{ISOOUT} = 100\text{ mA}$, $T_J = 150^\circ\text{C}$, $T_A \leq 80^\circ\text{C}$, $C_L = 15\text{ pF}$, input a 50-MHz 50% duty-cycle square wave			1.48	W
P_{D1}	Maximum power dissipation (side-1)				0.74	W
P_{D2}	Maximum power dissipation (side-2)				0.74	W

7.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance ⁽¹⁾	Shortest terminal-to-terminal distance through air	>8	mm
CPG	External creepage ⁽¹⁾	Shortest terminal-to-terminal distance across the package surface	>8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance – capacitive signal isolation)	> 17	μm
		Minimum internal gap (internal clearance – transformer power isolation)	>120	
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	> 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 300 V _{RMS}	I-IV	
		Rated mains voltage ≤ 600 V _{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V _{RMS}	I-III	
DIN VDE V 0884-11:2017-01 ⁽²⁾				
V _{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1500	V _{PK}
V _{IOWM}	Maximum working isolation voltage	AC voltage; Time dependent dielectric breakdown (TDDb) Test	1000	V _{RMS}
		DC voltage	1500	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} ; t = 60 s (qualification); V _{TEST} = 1.2 × V _{IOTM} ; t = 1 s (100% production)	7071	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ISOW774x ⁽³⁾	Test method per IEC 62368-1, 1.2/50 μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 10000 V _{PK} (qualification)	6250	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ISOW774xB ⁽³⁾	Test method per IEC 62368-1, 1.2/50 μs waveform, V _{TEST} = 1.3 × V _{IOSM} = 7800 V _{PK} (qualification)	6000	V _{PK}
q _{pd}	Apparent charge ⁽⁴⁾	Method a, after input/output safety test subgroup 2/3, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤ 5	pC
		Method a, after environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s; ISOW774x: V _{pd(m)} = 1.6 × V _{IORM} , t _m = 10 s, ISOW774xB: V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤ 5	
		Method b1, at routine test (100% production) and preconditioning (type test), V _{ini} = 1.2 × V _{IOTM} , t _{ini} = 1 s; ISOW774x: V _{pd(m)} = 1.875 × V _{IORM} , t _m = 1 s, ISOW774xB: V _{pd(m)} = 1.5 × V _{IORM} , t _m = 1 s	≤ 5	
C _{IO}	Barrier capacitance, input to output ⁽⁵⁾	V _{IO} = 0.4 × sin (2πft), f = 1 MHz	~3.5	pF
R _{IO}	Insulation resistance ⁽⁵⁾	V _{IO} = 500 V, T _A = 25°C	> 10 ¹²	Ω
		V _{IO} = 500 V, 100°C ≤ T _A ≤ 125°C	> 10 ¹¹	
		V _{IO} = 500 V, T _S = 150°C	> 10 ⁹	
	Pollution degree		2	
	Climatic category		40/125/21	
UL 1577				
V _{ISO(UL)}	Withstand isolation voltage	V _{TEST} = V _{ISO(UL)} = 5000 V _{RMS} , t = 60 s (qualification), V _{TEST} = 1.2 × V _{ISO(UL)} = 6000 V _{RMS} , t = 1 s (100% production)	5000	V _{RMS}

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.

- (2) ISOW77xx is suitable for *safe electrical insulation* and ISOW77xxB is suitable for *basic electrical insulation* only within the safety ratings.. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (4) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (5) All pins on each side of the barrier tied together creating a two-terminal device.

7.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV
Certified according to DIN VDE V 0884-11:2017-01	Certified according to IEC 62368-1, and IEC 60601-1	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1-2011	Certified according to EN 61010-1:2010/A1:2019 and EN 62368-1:2014
Reinforced insulation; Maximum transient isolation voltage, 7071 V _{PK} ; Maximum repetitive peak isolation voltage, 1500 V _{PK} ; Maximum surge isolation voltage, 6250 V _{PK} for ISOW774x (Reinforced), 6000 V _{PK} for ISOW774xB (Basic).	CSA 62368-1-19 and IEC 62368-1:2018 Ed. 3 and EN 62368-1:2020. (pollution degree 2, material group I) 600 V _{RMS} (ISOW774x Reinforced), 1000V _{RMS} (ISOW774xB Basic) maximum working voltage; 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed. 3+A1, 250 V _{RMS} maximum working voltage. Temperature rating is 90°C for reinforced insulation and 125°C for basic insulation; see certificate for details.	Single protection, 5000 V _{RMS}	Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate, 700 V _{RMS} maximum working voltage;	5000 V _{RMS} Reinforced insulation per EN 61010-1:2010 up to working voltage of 600 V _{RMS} ; 5000 V _{RMS} Reinforced insulation per EN 62368-1:2014 up to working voltage of 600 V _{RMS} (ISOW774x Reinforced), 1000 V _{RMS} (ISOW774xB Basic)
Certificate #: Reinforced: 40040142 Basic: 40047657	Master Contract#: 220991	File #: E181974	Certificate #: CQC21001297517	Client ID: 77311

7.8 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S	Safety input, output, or supply current ⁽¹⁾	R _{θJA} = 68.5°C/W, V _I = 5.5 V, T _J = 150°C, T _A = 25°C			332	mA
		R _{θJA} = 68.5°C/W, V _I = 3.6 V, T _J = 150°C, T _A = 25°C			507	
P _S	Safety input, output, or total power ⁽¹⁾	R _{θJA} = 68.5°C/W, T _J = 150°C, T _A = 25°C			1825	mW
T _S	Maximum safety temperature ⁽¹⁾				150	°C

- (1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.
The junction-to-air thermal resistance, R_{θJA}, in the Thermal Information table is that of a device installed on a high-K test board for leaded surface-mount packages. Use the following equations to calculate the value for each parameter:
T_J = T_A + R_{θJA} × P, where P is the power dissipated in the device.
T_{J(max)} = T_S = T_A + R_{θJA} × P_S, where T_{J(max)} is the maximum allowed junction temperature.
P_S = I_S × V_I, where V_I is the maximum input voltage.

7.9 Electrical Characteristics - Power Converter

$V_{DD} = 5\text{ V} \pm 10\%$ or $3.3\text{ V} \pm 10\%$ and V_{ISOIN} power externally, GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{DD} = 5\text{ V}$, $V_{ISOOUT} = 5\text{ V}$, $V_{SEL} = V_{ISOOUT}$						
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 55 mA	4.75	5	5.25	V
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 110 mA	4.5	5	5.25	V
$V_{ISOOUT}(\text{LINE})$	DC line regulation	$I_{ISOOUT} = 55\text{ mA}$, $V_{DD} = 4.5\text{ V}$ to 5.5 V		2		mV/V
$V_{ISOOUT}(\text{LOAD})$	DC load regulation	$I_{ISOOUT} = 0$ to 110 mA		1%		
EFF	Efficiency at maximum load current ⁽¹⁾	$I_{ISOOUT} = 110\text{ mA}$, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 10\text{ }\mu\text{F}$; $V_I = V_{DD}$ (ISOW774x); $V_I = 0\text{ V}$ (ISOW774x with F suffix).		46%		
$V_{ISOOUT}(\text{RIP})$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 20\text{ }\mu\text{F}$, $I_{ISOOUT} = 110\text{ mA}$		24		mV
I_{ISOOUT_SC}	DC current from V_{DD} supply under short circuit on V_{ISOOUT}	V_{ISOOUT} shorted to GND2		250		mA
$V_{DD} = 5\text{ V}$, $V_{ISOOUT} = 3.3\text{ V}$, $V_{SEL} = \text{GND2}$						
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 70 mA	3.135	3.3	3.465	V
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 140 mA	3.135	3.3	3.465	V
$V_{ISOOUT}(\text{LINE})$	DC line regulation	$I_{ISOOUT} = 70\text{ mA}$, $V_{DD} = 4.5\text{ V}$ to 5.5 V		2		mV/V
$V_{ISOOUT}(\text{LOAD})$	DC load regulation	$I_{ISOOUT} = 0$ to 140 mA		1%		
EFF	Efficiency at maximum load current ⁽¹⁾	$I_{ISOOUT} = 140\text{ mA}$, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 10\text{ }\mu\text{F}$; $V_I = V_{DD}$ (ISOW774x); $V_I = 0\text{ V}$ (ISOW774x with F suffix).		36%		
$V_{ISOOUT}(\text{RIP})$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 20\text{ }\mu\text{F}$, $I_{ISOOUT} = 110\text{ mA}$		30		mV
I_{ISOOUT_SC}	DC current from V_{DD} supply under short circuit on V_{ISOOUT}	V_{ISOOUT} shorted to GND2		250		mA
$V_{DD} = 3.3\text{ V}$, $V_{ISOOUT} = 3.3\text{ V}$, $V_{SEL} = \text{GND2}$						
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 30 mA	3.135	3.3	3.465	V
V_{ISOOUT}	Isolated supply voltage	External $I_{ISOOUT} = 0$ to 60 mA	3.135	3.3	3.465	V
$V_{ISOOUT}(\text{LINE})$	DC line regulation	$I_{ISOOUT} = 30\text{ mA}$, $V_{DD} = 3.0\text{ V}$ to 3.6 V		2		mV/V
$V_{ISOOUT}(\text{LOAD})$	DC load regulation	$I_{ISOOUT} = 0$ to 60 mA		1%		
EFF	Efficiency at maximum load current ⁽¹⁾	$I_{ISOOUT} = 60\text{ mA}$, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 10\text{ }\mu\text{F}$; $V_I = V_{DD}$ (ISOW774x); $V_I = 0\text{ V}$ (ISOW774x with F suffix).		43%		
$V_{ISOOUT}(\text{RIP})$	Output ripple on isolated supply (pk-pk)	20-MHz bandwidth, $C_{LOAD} = 0.01\text{ }\mu\text{F} \parallel 20\text{ }\mu\text{F}$, $I_{ISOOUT} = 60\text{ mA}$		14		mV
I_{ISOOUT_SC}	DC current from V_{DD} supply under short circuit on V_{ISOOUT}	V_{ISOOUT} shorted to GND2		185		mA

- (1) Power converter I_{LOAD} = current required to power the secondary side. I_{LOAD} does not take into account the channel isolator current. See Supply Current Characteristics Channel Isolator section for details.

7.10 Supply Current Characteristics - Power Converter

$V_{DD} = 5\text{ V} \pm 10\%$ or $3.3\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions unless otherwise noted).

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Power Converter Disabled							
Power converter supply current	EN/FLT = GND1, V _{ISOOUT} = No I _{LOAD}		I _{DD}		0.28	0.45	mA
Logic supply current	EN/FLT = GND1		I _{IO}		0.27	0.57	mA
Power Converter Enabled							
Power converter supply current input	V _{DD} = 5 V, V _{SEL} = V _{ISOOUT}	I _{LOAD} = 55 mA	I _{DD}		115	171	mA
	V _{DD} = 5 V, V _{SEL} = V _{ISOOUT}	I _{LOAD} = 110 mA			225	316	mA
	V _{DD} = 5 V, V _{SEL} = GND2	I _{LOAD} = 70 mA			127	169	mA
	V _{DD} = 5 V, V _{SEL} = GND2	I _{LOAD} = 140 mA			250	310	mA
	V _{DD} = 3.3 V, V _{SEL} = GND2	I _{LOAD} = 30 mA			74	112	mA
	V _{DD} = 3.3 V, V _{SEL} = GND2	I _{LOAD} = 60 mA			143	216	mA
Power converter output current ⁽¹⁾	V _{DD} = 5 V	V _{SEL} = V _{ISOOUT}	I _{ISOOUT}		110		mA
	V _{DD} = 5 V	V _{SEL} = GND2			140		mA
	V _{DD} = 3.3 V	V _{SEL} = GND2			60		mA

(1) I_{LOAD} does not take into account the channel isolator current. See Supply Current Characteristics Channel Isolator section for details.

7.11 Electrical Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 5\text{-V}$

V_{IO} , $V_{ISOIN} = 5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Channel Isolation					
V_{ITH}	Input pin rising threshold			$0.7 \times V_{SI}$	V
V_{ITL}	Input pin falling threshold			$0.3 \times V_{SI}$	V
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)			$0.1 \times V_{SI}$	V
I_{IL}	Low level input current	$V_{IL} = 0$ at INx		-25	μA
I_{IH}	High level input current	$V_{IH} = V_{SI}^{(1)}$ at INx		25	μA
V_{OH}	High level output voltage	$I_O = -4\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		$V_{SO}^{(1)} - 0.4$	V
V_{OL}	Low level output voltage	$I_O = 4\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		0.4	V
CMTI	Common mode transient immunity	$V_I = V_{SI}$ or 0 V , $V_{CM} = 1000\text{ V}$; see Common-Mode Transient Immunity Test Circuit	85	100	kV/us

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.12 Supply Current Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 5\text{-V}$

V_{IO} , $V_{ISOIN} = 5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISOW7740 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.5	3.6	mA
			I _{ISOIN}		4.6	6.9	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		2.5	3.6	mA
			I _{ISOIN}		4.6	6.9	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.5	3.6	mA
			I _{ISOIN}		4.6	6.9	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		6.9	9.2	mA
			I _{ISOIN}		4.8	7.2	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.7	6.4	mA
			I _{ISOIN}		4.8	7	mA
		10 Mbps	I _{DD_IO}		4.9	6.7	mA
			I _{ISOIN}		7.3	9.7	mA
		100 Mbps	I _{DD_IO}		6.5	8.4	mA
			I _{ISOIN}		31	35	mA
ISOW7741 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4.1	mA
			I _{ISOIN}		4.3	6.3	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4.1	mA
			I _{ISOIN}		4.3	6.3	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4.1	mA
			I _{ISOIN}		4.3	6.3	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		6.1	8.4	mA
			I _{ISOIN}		5.5	7.9	mA

ISOW7740, ISOW7741, ISOW7742, ISOW7743, ISOW7744

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 $V_{IO}, V_{ISOIN} = 5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.4	6.3	mA
			I _{ISOIN}		4.9	7.1	mA
		10 Mbps	I _{DD_IO}		5	7	mA
			I _{ISOIN}		6.3	8.9	mA
		100 Mbps	I _{DD_IO}		12.2	14.2	mA
			I _{ISOIN}		25	32	mA
ISOW7742 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.7	mA
			I _{ISOIN}		3.9	5.6	mA
			I _{DD_IO}		3.1	4.7	mA
			I _{ISOIN}		3.9	5.6	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.7	mA
			I _{ISOIN}		3.9	5.6	mA
			I _{DD_IO}		5.4	7.7	mA
			I _{ISOIN}		6.2	8.5	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.2	6.3	mA
			I _{ISOIN}		5.1	7.2	mA
		10 Mbps	I _{DD_IO}		5.5	7.6	mA
			I _{ISOIN}		6.3	8.3	mA
		100 Mbps	I _{DD_IO}		16.7	20	mA
			I _{ISOIN}		17.33	22	mA
ISOW7743 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.5	5.2	mA
			I _{ISOIN}		3.6	5.1	mA
			I _{DD_IO}		3.5	5.2	mA
			I _{ISOIN}		3.6	5.1	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.5	5.2	mA
			I _{ISOIN}		3.6	5.1	mA
			I _{DD_IO}		4.7	6.9	mA
			I _{ISOIN}		7	9.4	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4	6.2	mA
			I _{ISOIN}		5.3	7.2	mA
		10 Mbps	I _{DD_IO}		6	8.2	mA
			I _{ISOIN}		6.2	8	mA
		100 Mbps	I _{DD_IO}		24	27	mA
			I _{ISOIN}		14	17	mA
ISOW7744 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7744); V _I = 0 V (ISOW7744 with F suffix)		I _{DD_IO}		3.8	5.8	mA
			I _{ISOIN}		3.3	4.6	mA
			I _{DD_IO}		3.8	5.8	mA
			I _{ISOIN}		3.3	4.6	mA

V_{IO} , V_{ISOIN} = 5 V $\pm$ 10% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = V_{CCI} (ISOW7744); V_I = 0 V (ISOW7744 with F suffix)		I_{DD_IO}		3.8	5.8	mA
			I_{ISOIN}		3.3	4.6	mA
	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = 0 V (ISOW7744); V_I = V_{CCI} (ISOW7744 with F suffix)		I_{DD_IO}		4	6.2	mA
			I_{ISOIN}		7.7	10.2	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{DD_IO}		3.8	6.1	mA
			I_{ISOIN}		5.5	7.3	mA
		10 Mbps	I_{DD_IO}		6.4	8.6	mA
			I_{ISOIN}		5.6	7.3	mA
		100 Mbps	I_{DD_IO}		30	34	mA
			I_{ISOIN}		7.4	9	mA

(1) V_{CCI} = V_{IO} or V_{ISOIN}

7.13 Electrical Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 3.3\text{-V}$

V_{IO} , $V_{ISOIN} = 3.3\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Channel Isolation					
V_{ITH}	Input pin rising threshold			$0.7 \times V_{SI}$	V
V_{ITL}	Input pin falling threshold			$0.3 \times V_{SI}$	V
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)			$0.1 \times V_{SI}$	V
I_{IL}	Low level input current	$V_{IL} = 0$ at INx		-25	μA
I_{IH}	High level input current	$V_{IH} = V_{SI}^{(1)}$ at INx		25	μA
V_{OH}	High level output voltage	$I_O = -2\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		$V_{SO}^{(1)} - 0.3$	V
V_{OL}	Low level output voltage	$I_O = 2\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		0.3	V
CMTI	Common mode transient immunity	$V_I = V_{SI}$ or 0 V, $V_{CM} = 1000\text{ V}$; see Common-Mode Transient Immunity Test Circuit	85	100	kV/us

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.14 Supply Current Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 3.3\text{-V}$

V_{IO} , $V_{ISOIN} = 3.3\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISOW7740 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.5	mA
			I _{ISOIN}		4.6	6.9	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.5	mA
			I _{ISOIN}		4.5	6.9	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.5	mA
			I _{ISOIN}		4.5	6.9	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		6.8	9.1	mA
			I _{ISOIN}		4.8	7.2	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.6	6.4	mA
			I _{ISOIN}		4.7	7	mA
		10 Mbps	I _{DD_IO}		4.7	6.4	mA
			I _{ISOIN}		6	8.6	mA
		100 Mbps	I _{DD_IO}		5.5	7.8	mA
			I _{ISOIN}		22	30	mA
ISOW7741 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4	mA
			I _{ISOIN}		4.2	6.3	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.8	4	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		6.1	8.3	mA
			I _{ISOIN}		5.5	7.9	mA

V_{IO} , V_{ISOIN} = 3.3 V $\pm$ 10% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.4	6.3	mA
			I _{ISOIN}		4.9	7.1	mA
		10 Mbps	I _{DD_IO}		4.8	6.7	mA
			I _{ISOIN}		5.9	8.3	mA
		100 Mbps	I _{DD_IO}		9.4	12	mA
			I _{ISOIN}		17.5	25	mA
ISOW7742 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA
			I _{ISOIN}		3.9	5.5	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA
			I _{ISOIN}		3.9	5.5	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA
			I _{ISOIN}		3.9	5.5	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		5.4	7.6	mA
			I _{ISOIN}		6.2	8.5	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.2	6.3	mA
			I _{ISOIN}		5.1	7.2	mA
		10 Mbps	I _{DD_IO}		4.9	7	mA
			I _{ISOIN}		5.7	7.9	mA
		100 Mbps	I _{DD_IO}		13	16.6	mA
			I _{ISOIN}		13.7	17.5	mA
ISOW7743 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA
			I _{ISOIN}		3.6	5	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA
			I _{ISOIN}		3.6	5	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA
			I _{ISOIN}		3.6	5	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		4.7	6.8	mA
			I _{ISOIN}		6.9	9.3	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4	6.2	mA
			I _{ISOIN}		5.3	7.2	mA
		10 Mbps	I _{DD_IO}		5	7.4	mA
			I _{ISOIN}		5.6	7.6	mA
		100 Mbps	I _{DD_IO}		17	23	mA
			I _{ISOIN}		10.5	14	mA
ISOW7744 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7744); V _I = 0 V (ISOW7744 with F suffix)		I _{DD_IO}		3.7	5.7	mA
			I _{ISOIN}		3.2	4.5	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7744); V _I = V _{CCI} (ISOW7744 with F suffix)		I _{DD_IO}		3.7	5.7	mA
			I _{ISOIN}		3.2	4.5	mA

V_{IO} , V_{ISOIN} = 3.3 V $\pm$ 10% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = V_{CCI} (ISOW7744); V_I = 0 V (ISOW7744 with F suffix)		I_{DD_IO}		3.7	5.7	mA
			I_{ISOIN}		3.2	4.5	mA
	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = 0 V (ISOW7744); V_I = V_{CCI} (ISOW7744 with F suffix)		I_{DD_IO}		4	6.1	mA
			I_{ISOIN}		7.6	10.1	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{DD_IO}		3.8	6.1	mA
			I_{ISOIN}		5.5	7.3	mA
		10 Mbps	I_{DD_IO}		5.5	7.8	mA
			I_{ISOIN}		5.5	7.3	mA
		100 Mbps	I_{DD_IO}		21	29	mA
			I_{ISOIN}		6.3	8.3	mA

(1) V_{CCI} = V_{IO} or V_{ISOIN}

7.15 Electrical Characteristics Channel Isolator - $V_{IO}, V_{ISOIN} = 2.5\text{V}$

$V_{IO}, V_{ISOIN} = 2.5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Channel Isolation					
V_{ITH}	Input pin rising threshold			$0.7 \times V_{SI}$	V
V_{ITL}	Input pin falling threshold			$0.3 \times V_{SI}$	V
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)			$0.1 \times V_{SI}$	V
I_{IL}	Low level input current	$V_{IL} = 0$ at INx		-25	μA
I_{IH}	High level input current	$V_{IH} = V_{SI}^{(1)}$ at INx		25	μA
V_{OH}	High level output voltage	$I_O = -1\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		$V_{SO}^{(1)} - 0.1$	V
V_{OL}	Low level output voltage	$I_O = 1\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		0.1	V
CMTI	Common mode transient immunity	$V_I = V_{SI}$ or 0 V , $V_{CM} = 1000\text{ V}$; see Common-Mode Transient Immunity Test Circuit	85	100	kV/us

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.16 Supply Current Characteristics Channel Isolator - $V_{IO}, V_{ISOIN} = 2.5\text{V}$

$V_{IO}, V_{ISOIN} = 2.5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISOW7740 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.8	mA
			I _{ISOIN}		4.5	6.9	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.8	mA
			I _{ISOIN}		4.5	6.9	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		2.4	3.8	mA
			I _{ISOIN}		4.5	6.9	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		6.8	9	mA
			I _{ISOIN}		4.7	7.2	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.6	6.4	mA
			I _{ISOIN}		4.7	7	mA
		10 Mbps	I _{DD_IO}		4.7	6.4	mA
			I _{ISOIN}		5.7	8.1	mA
		100 Mbps	I _{DD_IO}		5.3	7.2	mA
			I _{ISOIN}		18	24	mA
ISOW7741 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.7	4.3	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		2.7	4.3	mA
			I _{ISOIN}		4.2	6.3	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.7	4.3	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		6.1	8.3	mA
			I _{ISOIN}		5.4	7.9	mA

ISOW7740, ISOW7741, ISOW7742, ISOW7743, ISOW7744

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 $V_{IO}, V_{ISOIN} = 2.5\text{ V} \pm 10\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT	
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.4	6.3	mA	
			I _{ISOIN}		4.9	7.1	mA	
		10 Mbps	I _{DD_IO}		4.7	8.3	mA	
			I _{ISOIN}		5.6	7.9	mA	
		100 Mbps	I _{DD_IO}		8.2	11.2	mA	
			I _{ISOIN}		14.6	18.8	mA	
ISOW7742 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA	
			I _{ISOIN}		3.8	5.5	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA
				I _{ISOIN}		3.8	5.5	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		3.1	4.6	mA	
			I _{ISOIN}		3.8	5.4	mA	
		EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		5.3	7.5	mA
				I _{ISOIN}		6.1	8.4	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.2	6.3	mA	
			I _{ISOIN}		5.1	7.2	mA	
		10 Mbps	I _{DD_IO}		4.7	6.8	mA	
			I _{ISOIN}		5.6	7.7	mA	
		100 Mbps	I _{DD_IO}		10.9	14.5	mA	
			I _{ISOIN}		11.7	15.5	mA	
ISOW7743 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA	
			I _{ISOIN}		3.5	4.9	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA
				I _{ISOIN}		3.5	4.9	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.4	5.1	mA	
			I _{ISOIN}		3.5	4.9	mA	
		EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		4.6	6.7	mA
				I _{ISOIN}		6.8	9.3	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4	6.2	mA	
			I _{ISOIN}		5.3	7.2	mA	
		10 Mbps	I _{DD_IO}		4.8	7	mA	
			I _{ISOIN}		5.6	7.5	mA	
		100 Mbps	I _{DD_IO}		13.8	17	mA	
			I _{ISOIN}		8.3	13	mA	
ISOW7744 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7744); V _I = 0 V (ISOW7744 with F suffix)		I _{DD_IO}		3.7	5.9	mA	
			I _{ISOIN}		3.2	4.4	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7744); V _I = V _{CCI} (ISOW7744 with F suffix)		I _{DD_IO}		3.7	5.7	mA
				I _{ISOIN}		3.2	4.4	mA

V_{IO} , V_{ISOIN} = 2.5 V $\pm$ 10% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = V_{CCI} (ISOW7744); V_I = 0 V (ISOW7744 with F suffix)		I_{DD_IO}		3.7	5.7	mA
			I_{ISOIN}		3.2	4.4	mA
	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = 0 V (ISOW7744); V_I = V_{CCI} (ISOW7744 with F suffix)		I_{DD_IO}		3.9	6.2	mA
			I_{ISOIN}		7.5	10	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{DD_IO}		3.8	6.1	mA
			I_{ISOIN}		5.5	7.3	mA
		10 Mbps	I_{DD_IO}		4.8	7.2	mA
			I_{ISOIN}		5.5	7.3	mA
		100 Mbps	I_{DD_IO}		16.5	22	mA
			I_{ISOIN}		6	8.1	mA

(1) V_{CCI} = V_{IO} or V_{ISOIN}

7.17 Electrical Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 1.8\text{-V}$

V_{IO} , $V_{ISOIN} = 1.8\text{ V} \pm 5\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Channel Isolation					
V_{ITH}	Input pin rising threshold		$0.7 \times V_{SI}$		V
V_{ITL}	Input pin falling threshold	$0.3 \times V_{SI}$			V
$V_{I(HYS)}$	Input pin threshold hysteresis (INx)	$0.1 \times V_{SI}$			V
I_{IL}	Low level input current	$V_{IL} = 0$ at INx	-25		μA
I_{IH}	High level input current	$V_{IH} = V_{SI}^{(1)}$ at INx		25	μA
V_{OH}	High level output voltage	$I_O = -1\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms	$V_{SO}^{(1)} - 0.1$		V
V_{OL}	Low level output voltage	$I_O = 1\text{ mA}$, see Switching Characteristics Test Circuit and Voltage Waveforms		0.1	V
CMTI	Common mode transient immunity	$V_I = V_{SI}$ or 0 V, $V_{CM} = 1000\text{ V}$; see Common-Mode Transient Immunity Test Circuit	85	100	kV/us

(1) V_{SI} = input side supply; V_{SO} = output side supply

7.18 Supply Current Characteristics Channel Isolator - V_{IO} , $V_{ISOIN} = 1.8\text{-V}$

V_{IO} , $V_{ISOIN} = 1.8\text{ V} \pm 5\%$ GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISOW7740 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		1.9	3	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		1.9	3	mA
			I _{ISOIN}		4.2	6.3	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7740); V _I = 0 V (ISOW7740 with F suffix)		I _{DD_IO}		1.9	3	mA
			I _{ISOIN}		4.2	6.3	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7740); V _I = V _{CCI} (ISOW7740 with F suffix)		I _{DD_IO}		6.1	8.7	mA
			I _{ISOIN}		4.4	6.7	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.0	6.4	mA
			I _{ISOIN}		4.7	7	mA
		10 Mbps	I _{DD_IO}		4.0	6.4	mA
			I _{ISOIN}		5.4	7.7	mA
		100 Mbps	I _{DD_IO}		4.6	9.5	mA
			I _{ISOIN}		14.6	19	mA
ISOW7741 Channel Supply Current							
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.4	3.6	mA
			I _{ISOIN}		3.8	5.6	mA
	EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		2.4	3.6	mA
			I _{ISOIN}		3.8	5.6	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7741); V _I = 0 V (ISOW7741 with F suffix)		I _{DD_IO}		2.4	3.6	mA
			I _{ISOIN}		3.8	5.6	mA
	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7741); V _I = V _{CCI} (ISOW7741 with F suffix)		I _{DD_IO}		5.5	7.8	mA
			I _{ISOIN}		4.9	7.3	mA

V_{IO} , V_{ISOIN} = 1.8 V $\pm$ 5% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT	
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4	5.7	mA	
			I _{ISOIN}		4.4	6.5	mA	
		10 Mbps	I _{DD_IO}		4.2	6	mA	
			I _{ISOIN}		5.2	7.3	mA	
		100 Mbps	I _{DD_IO}		6.9	9.6	mA	
			I _{ISOIN}		12	15.8	mA	
ISOW7742 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		2.8	4.3	mA	
			I _{ISOIN}		3.4	5.1	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		2.8	4.3	mA
				I _{ISOIN}		3.4	5.1	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7742); V _I = 0 V (ISOW7742 with F suffix)		I _{DD_IO}		2.8	4.3	mA	
			I _{ISOIN}		3.4	5.1	mA	
		EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7742); V _I = V _{CCI} (ISOW7742 with F suffix)		I _{DD_IO}		5	7.4	mA
				I _{ISOIN}		5.6	8.1	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4.2	6.3	mA	
			I _{ISOIN}		4.5	7.2	mA	
		10 Mbps	I _{DD_IO}		4.3	6.6	mA	
			I _{ISOIN}		5.0	7.5	mA	
		100 Mbps	I _{DD_IO}		9.1	12.5	mA	
			I _{ISOIN}		9.7	13.3	mA	
ISOW7743 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.2	5	mA	
			I _{ISOIN}		3	4.5	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		3.2	5	mA
				I _{ISOIN}		3	4.5	mA
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V _{CCI} ; V _I = V _{CCI} (ISOW7743); V _I = 0 V (ISOW7743 with F suffix)		I _{DD_IO}		3.2	5	mA	
			I _{ISOIN}		3	4.5	mA	
		EN_IO1 = EN_IO2 = V _{CCI} ; V _I = 0 V (ISOW7743); V _I = V _{CCI} (ISOW7743 with F suffix)		I _{DD_IO}		4.4	6.6	mA
				I _{ISOIN}		6.2	8.9	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C _L = 15 pF	1 Mbps	I _{DD_IO}		4	6.2	mA	
			I _{ISOIN}		4.6	7.2	mA	
		10 Mbps	I _{DD_IO}		4.6	6.7	mA	
			I _{ISOIN}		4.9	7.4	mA	
		100 Mbps	I _{DD_IO}		11.4	15	mA	
			I _{ISOIN}		7.8	9.8	mA	
ISOW7744 Channel Supply Current								
Supply current - Disable	EN_IO1 = EN_IO2 = 0 V; V _I = V _{CCI} ⁽¹⁾ (ISOW7744); V _I = 0 V (ISOW7744 with F suffix)		I _{DD_IO}		3.6	5.7	mA	
			I _{ISOIN}		2.6	3.8	mA	
		EN_IO1 = EN_IO2 = 0 V; V _I = 0 V (ISOW7744); V _I = V _{CCI} (ISOW7744 with F suffix)		I _{DD_IO}		3.6	5.7	mA
				I _{ISOIN}		2.6	3.8	mA

V_{IO} , V_{ISOIN} = 1.8 V $\pm$ 5% GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions, unless otherwise specified)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Channel Supply current - DC signal	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = V_{CCI} (ISOW7744); V_I = 0 V (ISOW7744 with F suffix)		I_{DD_IO}		3.6	5.7	mA
			I_{ISOIN}		2.6	3.8	mA
	EN_IO1 = EN_IO2 = V_{CCI} ; V_I = 0 V (ISOW7744); V_I = V_{CCI} (ISOW7744 with F suffix)		I_{DD_IO}		3.8	6.1	mA
			I_{ISOIN}		6.7	9.6	mA
Channel Supply current - AC signal	All channels switching with square wave clock input; C_L = 15 pF	1 Mbps	I_{DD_IO}		3.8	6.1	mA
			I_{ISOIN}		4.7	7.3	mA
		10 Mbps	I_{DD_IO}		4.5	7	mA
			I_{ISOIN}		4.7	7.3	mA
		100 Mbps	I_{DD_IO}		13.8	16.9	mA
			I_{ISOIN}		5.2	7.7	mA

(1) V_{CCI} = V_{IO} or V_{ISOIN}

7.19 Switching Characteristics - 5-V Supply

$V_{ISOIN} = 5\text{ V} \pm 10\%$, $V_{IO} = 5\text{ V} \pm 10\%$, GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Switching Characteristics Test Circuit and Voltage Waveforms	7.6	10.7	15.7	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.9	5	ns
$ENIO_t_{PLH}$, $ENIO_t_{PHL}$	ENIO propagation delay time (opposite side)	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		210	473.8	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			4	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				5.5	ns
t_r	Output signal rise time	See Switching Characteristics Test Circuit and Voltage Waveforms		2.5	3.6	ns
t_f	Output signal fall time			2.4	3.5	ns
t_{PHZ}	Channel disable propagation delay, high-to-high impedance output	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		217	286	ns
t_{PLZ}	Channel disable propagation delay, low-to-high impedance output			217	286	ns
t_{PZH}	Channel enable propagation delay, high impedance-to-high output for ISOW774x			237	333	ns
	Channel enable propagation delay, high impedance-to-high output for ISOW774x with F suffix			237	333	ns
t_{PZL}	Channel enable propagation delay, high impedance-to-low output for ISOW774x			237	333	ns
	Channel enable propagation delay, high impedance-to-low output for ISOW774x with F suffix			237	333	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{IO} or V_{ISOIN} goes below 1.6 V at 10 mV/ns. See Default Output Delay Time Test Circuit and Voltage Waveforms		0.1	0.3	μs
t_{ie}	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.7		ns

(1) Also known as pulse skew.

(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.20 Switching Characteristics - 3.3-V Supply

$V_{ISOIN} = 3.3\text{ V} \pm 10\%$, $V_{IO} = 3.3\text{ V} \pm 10\%$, GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Switching Characteristics Test Circuit and Voltage Waveforms	6	11	16.2	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.6	4.7	ns
$ENIO_t_{PLH}$, $ENIO_t_{PHL}$	ENIO propagation delay time (opposite side)	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		220	474	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			4.1	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				4.5	ns
t_r	Output signal rise time	See Switching Characteristics Test Circuit and Voltage Waveforms		1.8	2.7	ns
t_f	Output signal fall time			1.6	2.4	ns
t_{PHZ}	Channel disable propagation delay, high-to-high impedance output	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		230	300.4	ns
t_{PLZ}	Channel disable propagation delay, low-to-high impedance output			230	299.6	ns
t_{PZH}	Channel enable propagation delay, high impedance-to-high output for ISOW774x			226	318.9	ns
	Channel enable propagation delay, high impedance-to-high output for ISOW774x with F suffix			226	319.1	ns
t_{PZL}	Channel enable propagation delay, high impedance-to-low output for ISOW774x			225	317.9	ns
	Channel enable propagation delay, high impedance-to-low output for ISOW774x with F suffix			225	317.6	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{IO} or V_{ISOIN} goes below 1.6 V at 10 mV/ns. See Default Output Delay Time Test Circuit and Voltage Waveforms		0.1	0.3	μ s
t_{ie}	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.65		ns

(1) Also known as pulse skew.

(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.21 Switching Characteristics - 2.5-V Supply

$V_{ISOIN} = 2.5\text{ V} \pm 10\%$, $V_{IO} = 2.5\text{ V} \pm 10\%$, GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Switching Characteristics Test Circuit and Voltage Waveforms	7.5	12	18	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.36	5.1	ns
$ENIO_t_{PLH}$, $ENIO_t_{PHL}$	ENIO propagation delay time (opposite side)	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		225	478	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			4.1	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				6	ns
t_r	Output signal rise time	See Switching Characteristics Test Circuit and Voltage Waveforms		2	3.26	ns
t_f	Output signal fall time			1.8	3.2	ns
t_{PHZ}	Channel disable propagation delay, high-to-high impedance output	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		237	326	ns
t_{PLZ}	Channel disable propagation delay, low-to-high impedance output			236	325	ns
t_{PZH}	Channel enable propagation delay, high impedance-to-high output for ISOW774x			228	360	ns
	Channel enable propagation delay, high impedance-to-high output for ISOW774x with F suffix			228	360	ns
t_{PZL}	Channel enable propagation delay, high impedance-to-low output for ISOW774x			227	350	ns
	Channel enable propagation delay, high impedance-to-low output for ISOW774x with F suffix			227	350	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{IO} or V_{ISOIN} goes below 1.6 V at 10 mV/ns. See Default Output Delay Time Test Circuit and Voltage Waveforms		0.1	0.3	μ s
t_{ie}	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.7		ns

(1) Also known as pulse skew.

(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.22 Switching Characteristics - 1.8-V Supply

$V_{IS0IN} = 1.8\text{ V} \pm 5\%$, $V_{IO} = 1.8\text{ V} \pm 5\%$, GND1 = GNDIO, GND2 = GISOIN (over recommended operating conditions unless otherwise noted)

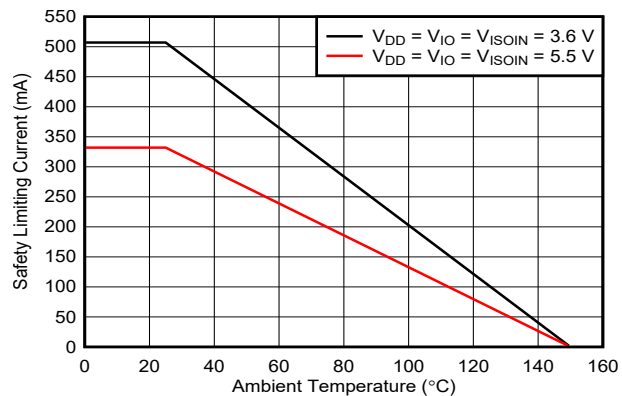
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Switching Characteristics Test Circuit and Voltage Waveforms	7.5	15	21.5	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0	5.8	ns
$ENIO_t_{PLH}$, $ENIO_t_{PHL}$	ENIO propagation delay time (opposite side)	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		243	475	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			4.1	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				8.6	ns
t_r	Output signal rise time	See Switching Characteristics Test Circuit and Voltage Waveforms		1.9	3	ns
t_f	Output signal fall time			1.8	3	ns
t_{PHZ}	Channel disable propagation delay, high-to-high impedance output	See Enable/Disable Propagation Delay Time Test Circuit and Waveform		260	410	ns
t_{PLZ}	Channel disable propagation delay, low-to-high impedance output			260	406	ns
t_{PZH}	Channel enable propagation delay, high impedance-to-high output for ISOW774x			240	444	ns
	Channel enable propagation delay, high impedance-to-high output for ISOW774x with F suffix			240	444	ns
t_{PZL}	Channel enable propagation delay, high impedance-to-low output for ISOW774x			237	439	ns
	Channel enable propagation delay, high impedance-to-low output for ISOW774x with F suffix			237	439	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{IO} or V_{IS0IN} goes below 1.6 V at 10 mV/ns. See Default Output Delay Time Test Circuit and Voltage Waveforms		0.1	0.3	μ s
t_{ie}	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.7		ns

(1) Also known as pulse skew.

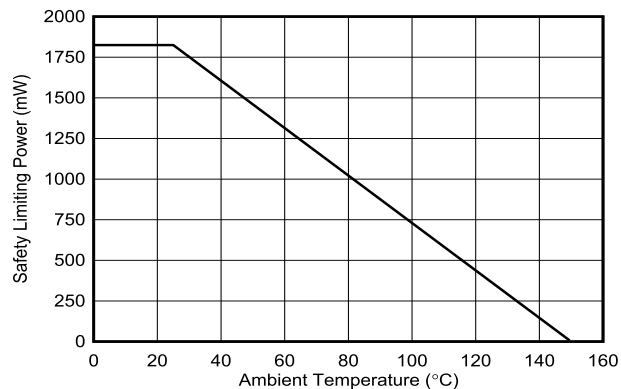
(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

7.23 Insulation Characteristics Curves

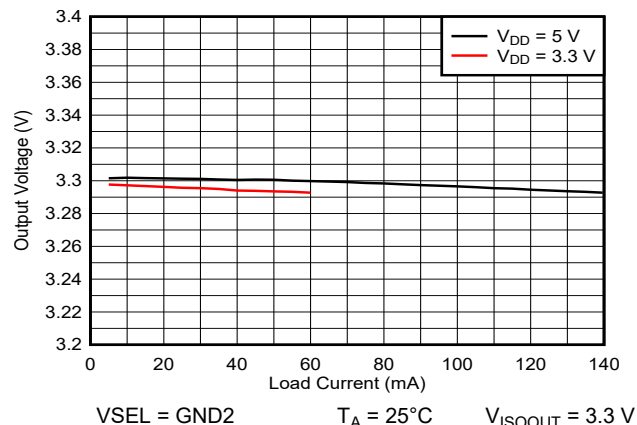


7-1. Thermal Derating Curve for Safety Limiting Current for DFM-20 Package

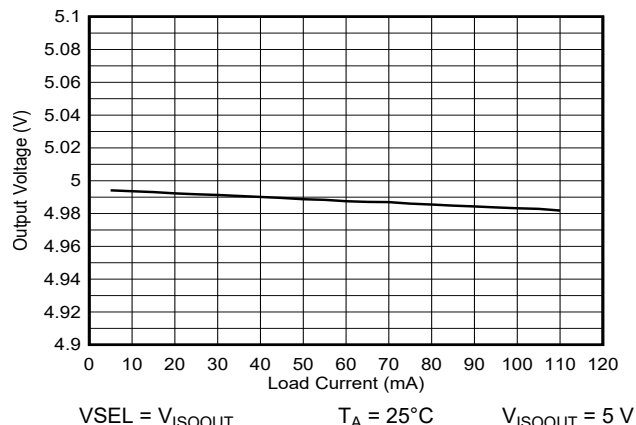


7-2. Thermal Derating Curve for Safety Limiting Power for DFM-20 Package

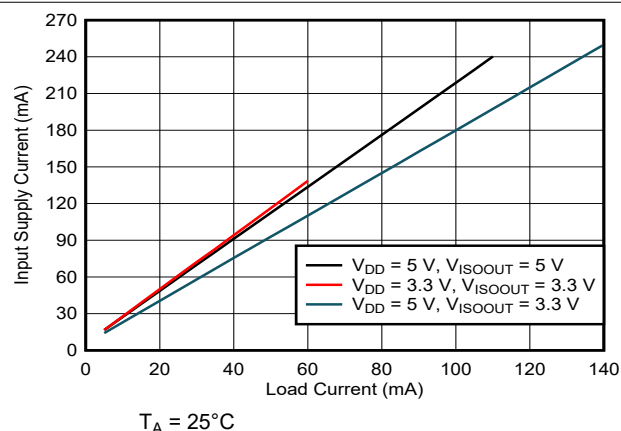
7.24 Typical Characteristics



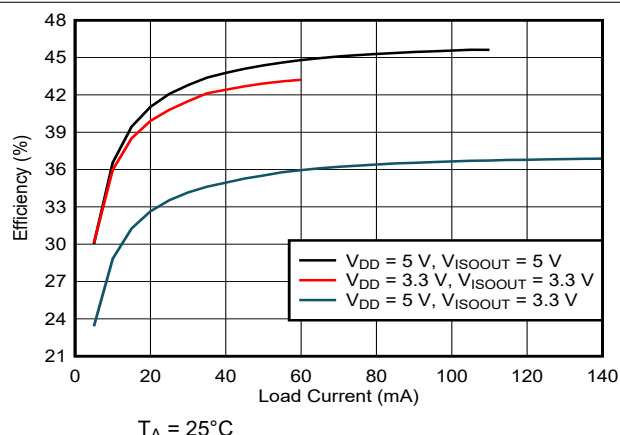
7-3. Isolated Supply Voltage (V_{ISOOUT}) vs Load Current (I_{ISOOUT})



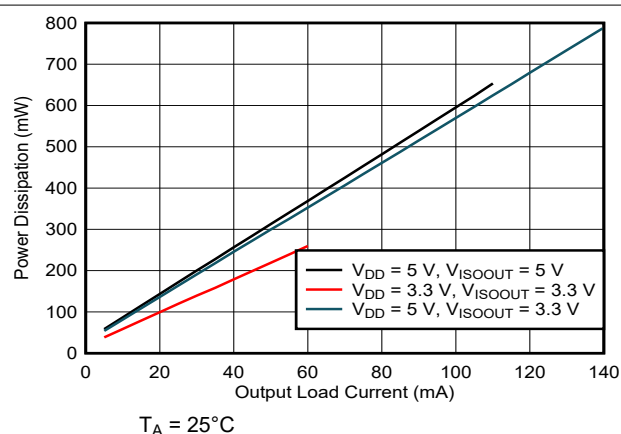
7-4. Isolated Supply Voltage (V_{ISOOUT}) vs Load Current (I_{ISOOUT})



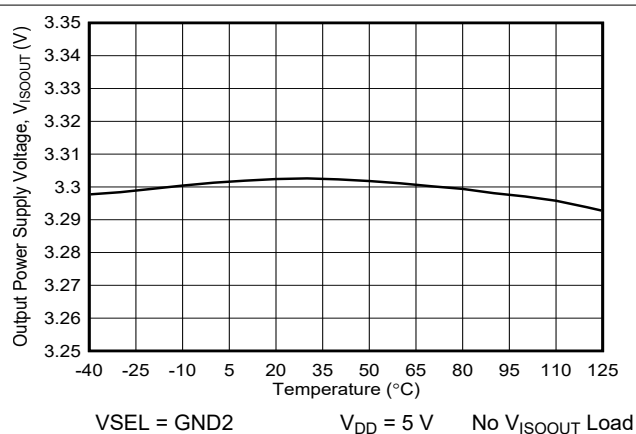
7-5. Supply Current (I_{DD}) vs Load Current (I_{ISOOUT})



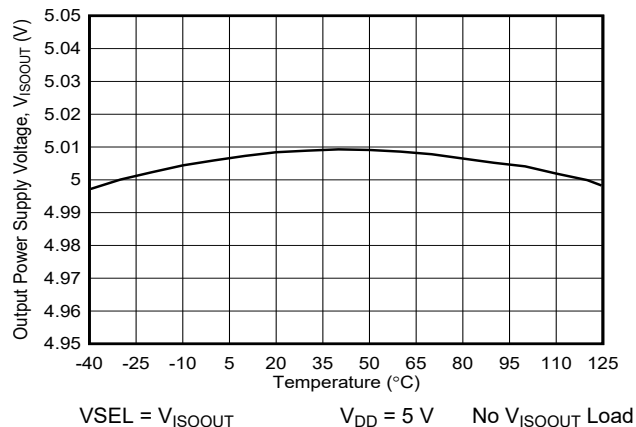
7-6. Efficiency vs Load Current (I_{ISOOUT})



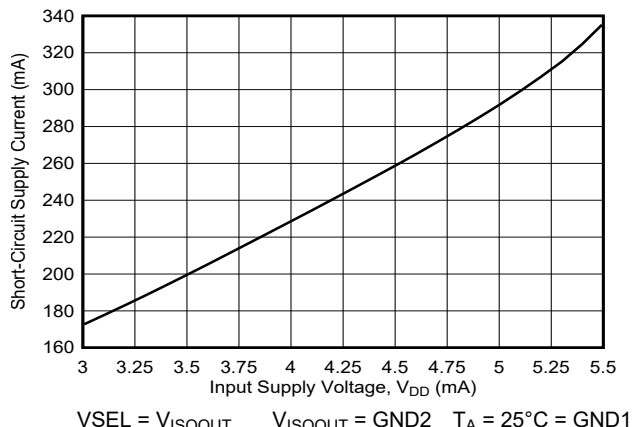
7-7. Power Dissipation vs Load Current (I_{ISOOUT})



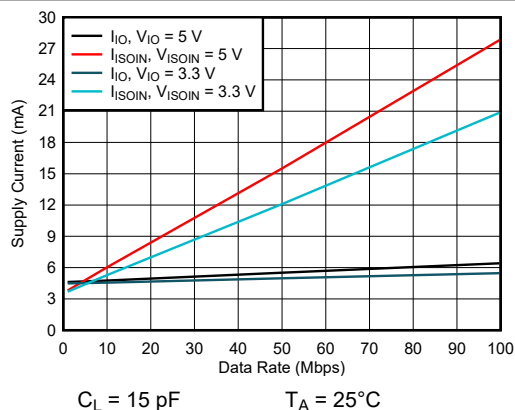
7-8. 3.3-V Isolated Supply Voltage (V_{ISOOUT}) vs Free-Air Temperature



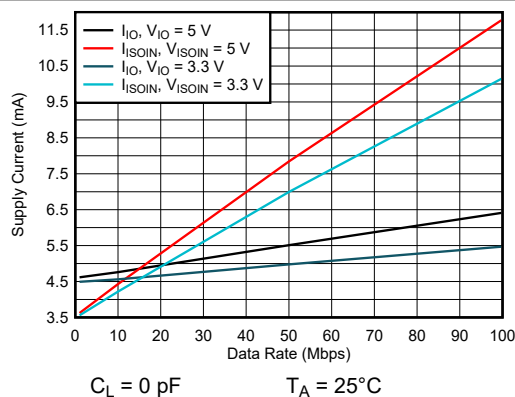
7-9. 5-V Isolated Supply Voltage (V_{ISOOUT}) vs Free-Air Temperature



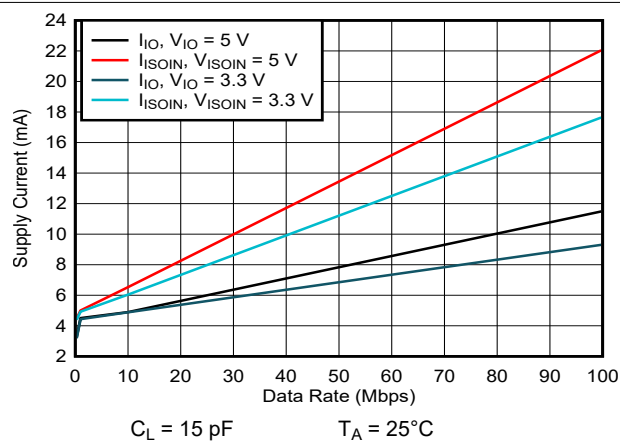
7-10. Short-Circuit Supply Current (I_{CC}) vs Supply Voltage (V_{CC})



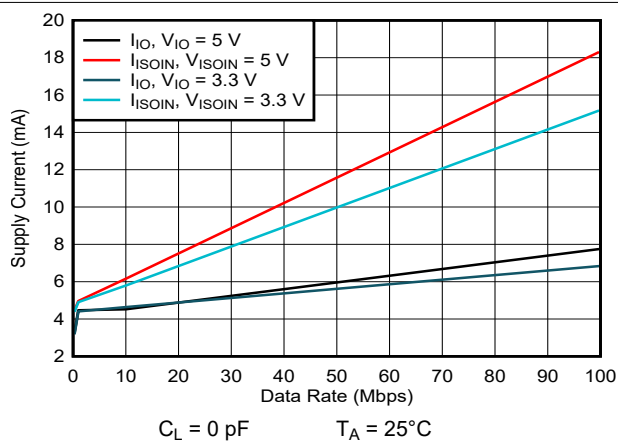
7-11. ISOW7740 Channel Supply Currents vs Data Rate For $C_L = 15$ pF



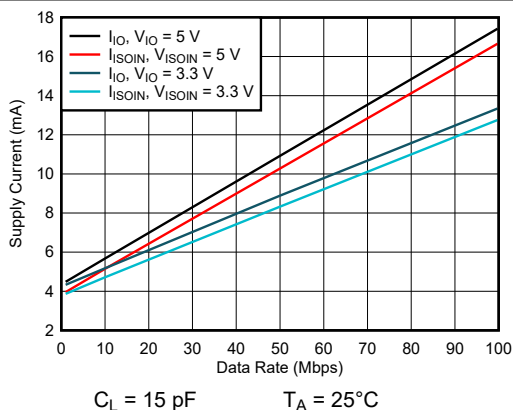
7-12. ISOW7740 Channel Supply Currents vs Data Rate For $C_L = 0$ pF



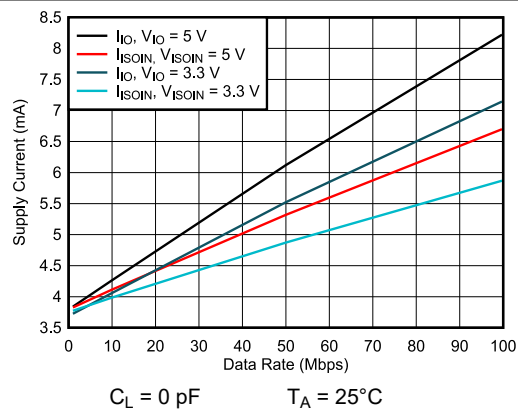
7-13. ISOW7741 Channel Supply Currents vs Data Rate For $C_L = 15$ pF



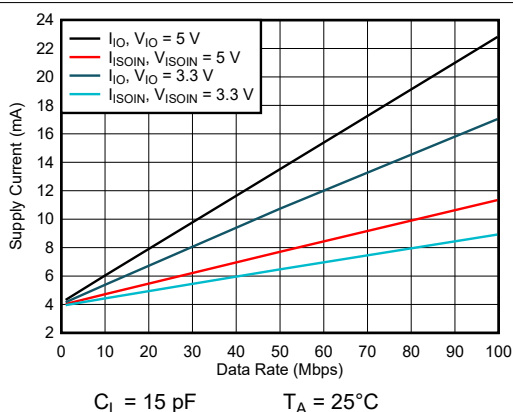
7-14. ISOW7741 Channel Supply Currents vs Data Rate For $C_L = 0$ pF



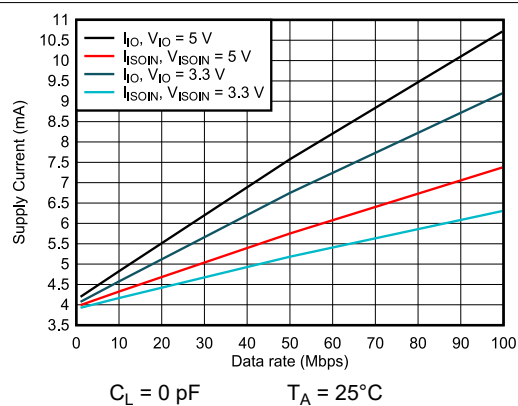
7-15. ISOW7742 Channel Supply Currents vs Data Rate For $C_L = 15 \text{ pF}$



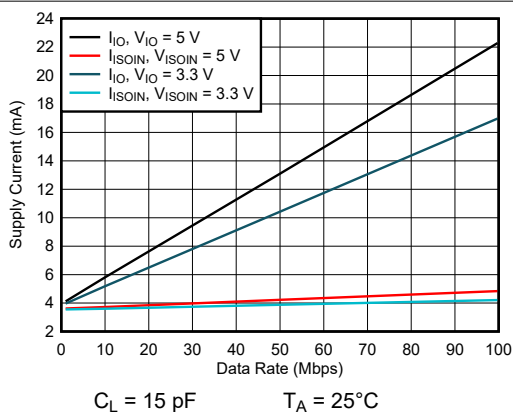
7-16. ISOW7742 Channel Supply Currents vs Data Rate For $C_L = 0 \text{ pF}$



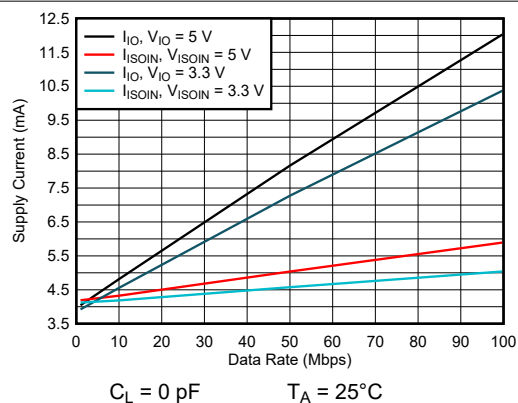
7-17. ISOW7743 Channel Supply Currents vs Data Rate For $C_L = 15 \text{ pF}$



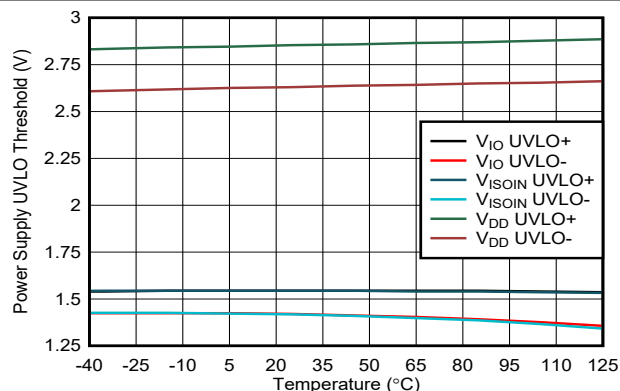
7-18. ISOW7743 Channel Supply Currents vs Data Rate For $C_L = 0 \text{ pF}$



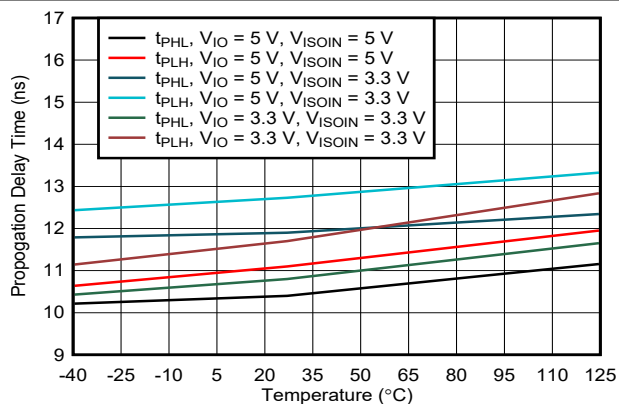
7-19. ISOW7744 Channel Supply Currents vs Data Rate For $C_L = 15 \text{ pF}$



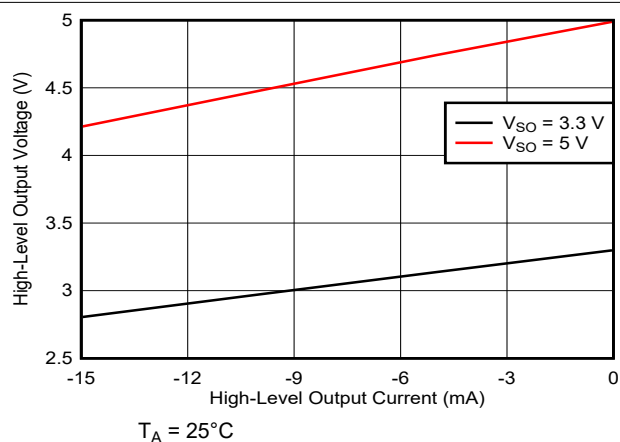
7-20. ISOW7744 Channel Supply Currents vs Data Rate For $C_L = 0 \text{ pF}$



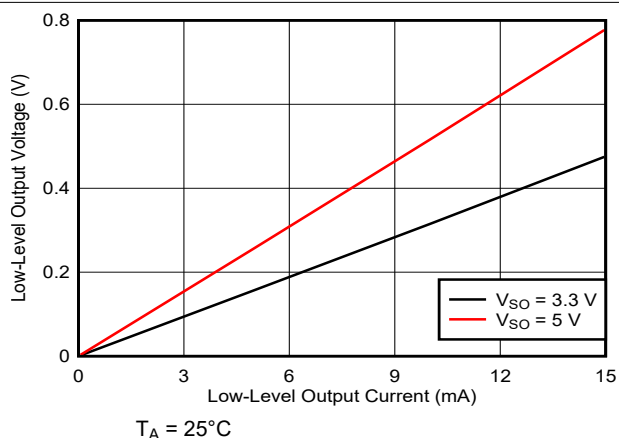
7-21. Power-Supply Undervoltage Threshold vs Free Air Temperature



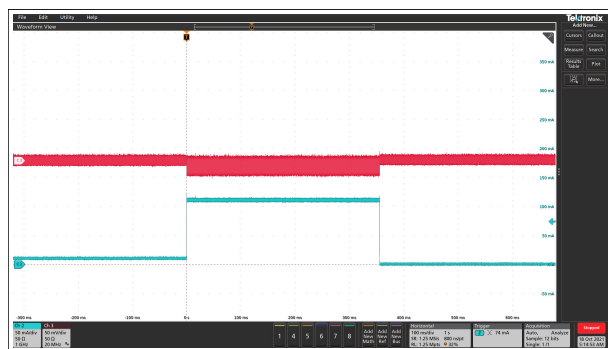
7-22. Propagation Delay Time vs Free-Air Temperature



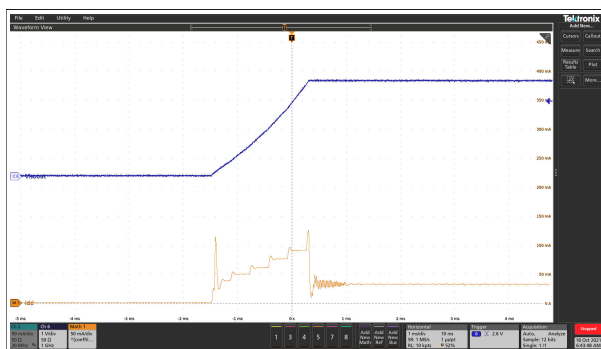
7-23. High-Level Output Voltage vs High-Level Output Current



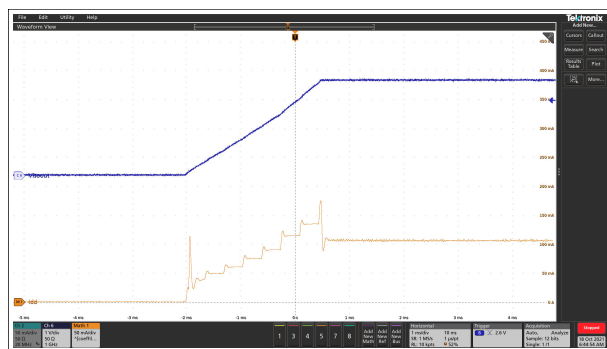
7-24. Low-Level Output Voltage vs Low-Level Output Current



7-25. 10-mA to 110-mA Load Transient Response

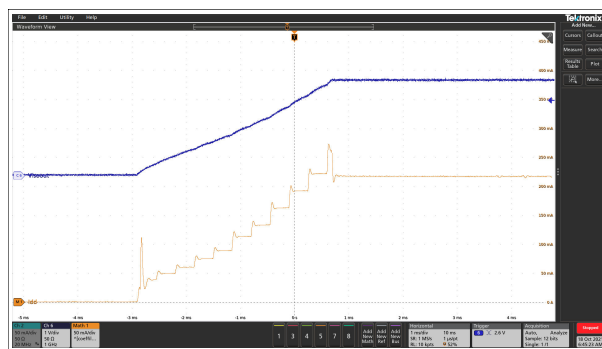


7-26. Soft Start at 10-mA Load For $V_{ISOOUT} = 3.3$ V



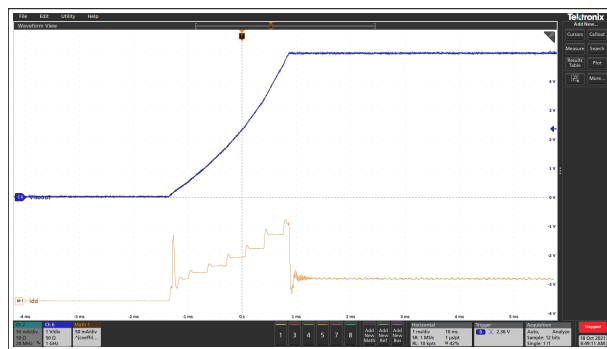
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 3.3\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-27. Soft Start at 50-mA Load For $V_{ISOOUT} = 3.3\text{ V}$



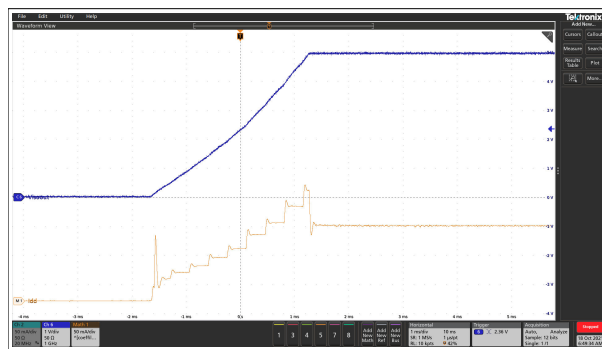
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 3.3\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-28. Soft Start at 110-mA Load For $V_{ISOOUT} = 3.3\text{ V}$



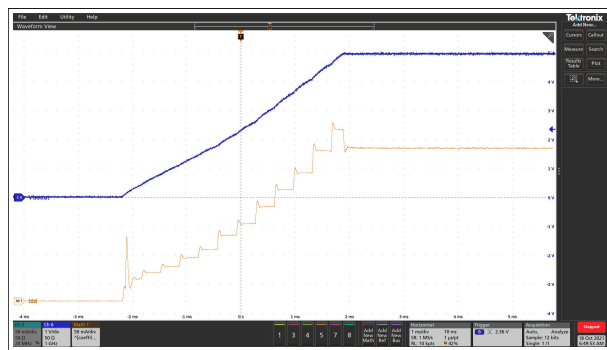
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 5\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-29. Soft Start at 10-mA Load For $V_{ISOOUT} = 5\text{ V}$



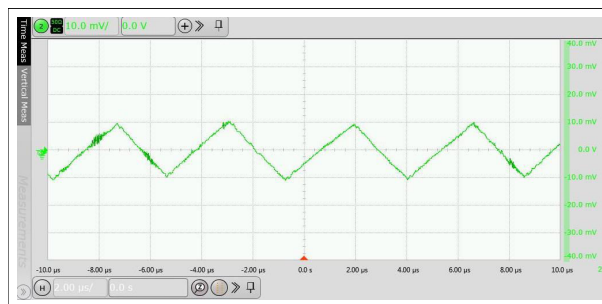
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 5\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-30. Soft Start at 50-mA Load For $V_{ISOOUT} = 5\text{ V}$



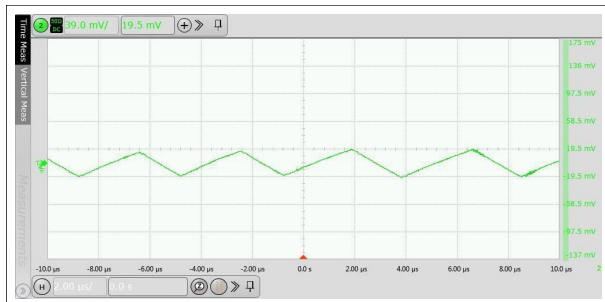
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 5\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-31. Soft Start at 110-mA Load For $V_{ISOOUT} = 5\text{ V}$



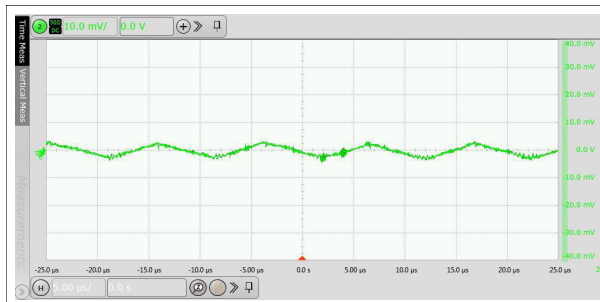
$V_{DD} = 3.3\text{ V}$ $V_{ISOOUT} = 3.3\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-32. V_{ISOOUT} Ripple Voltage at 3.3 V with 10 μF Capacitor and 60 mA load



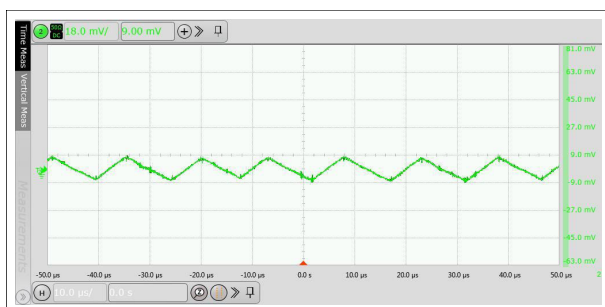
$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 5\text{ V}$ 10 μF
Capacitor on
 V_{ISOOUT}

7-33. V_{ISOOUT} Ripple Voltage at 5 V with 10 μF Capacitor and 110 mA load



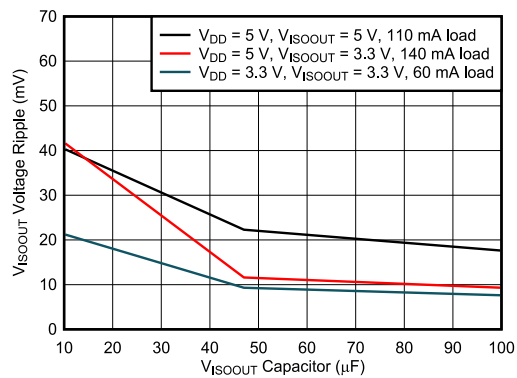
$V_{DD} = 3.3\text{ V}$ $V_{ISOOUT} = 3.3\text{ V}$ 100 μF
Capacitor on
 V_{ISOOUT}

7-34. V_{ISOOUT} Ripple Voltage at 3.3 V with 100 μF Capacitor and 60 mA load



$V_{DD} = 5\text{ V}$ $V_{ISOOUT} = 5\text{ V}$ 100 μF
Capacitor on
 V_{ISOOUT}

7-35. V_{ISOOUT} Ripple Voltage at 5 V with 100 μF Capacitor and 110 mA load

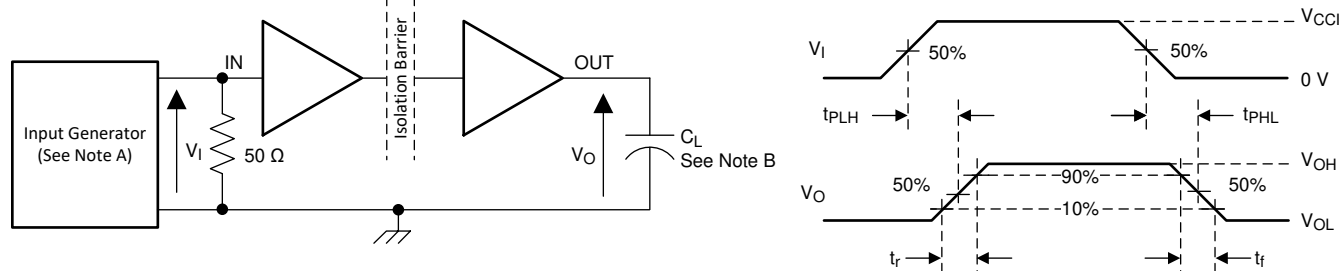


$T_A = 25^\circ\text{C}$

7-36. V_{ISOOUT} Ripple Voltage vs Load Capacitor

8 Parameter Measurement Information

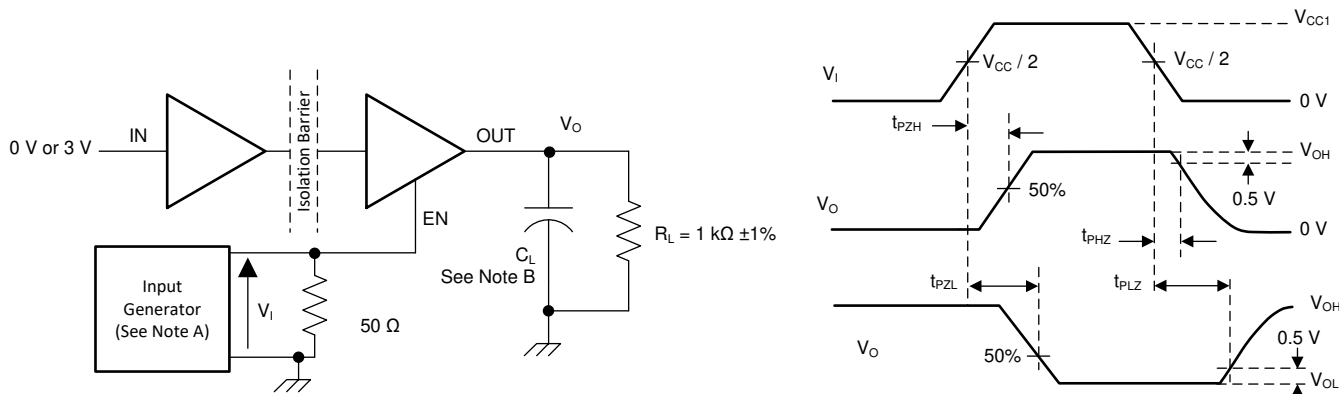
In the below images, V_{CCI} and V_{CCO} refers to the power supplies V_{IO} and V_{ISOIN} , respectively.



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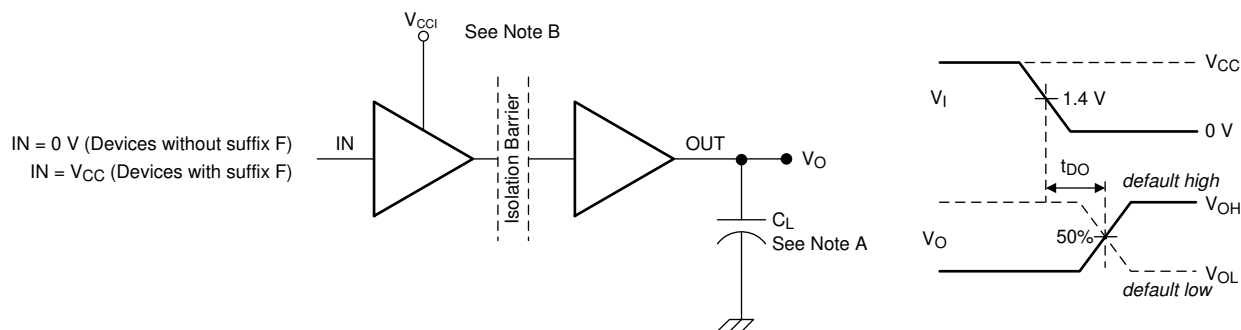
- A. $C_L = 15$ pF and The input pulse is supplied by a generator having the following characteristics: $PRR \leq 50$ kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$. At the input, 50Ω resistor is required to terminate Input Generator signal. It is not needed in actual application.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

8-1. Switching Characteristics Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: $PRR \leq 50$ kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$. At the input, 50Ω resistor is required to terminate Input Generator signal. It is not needed in actual application.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

8-2. Enable/Disable Propagation Delay Time Test Circuit and Waveform



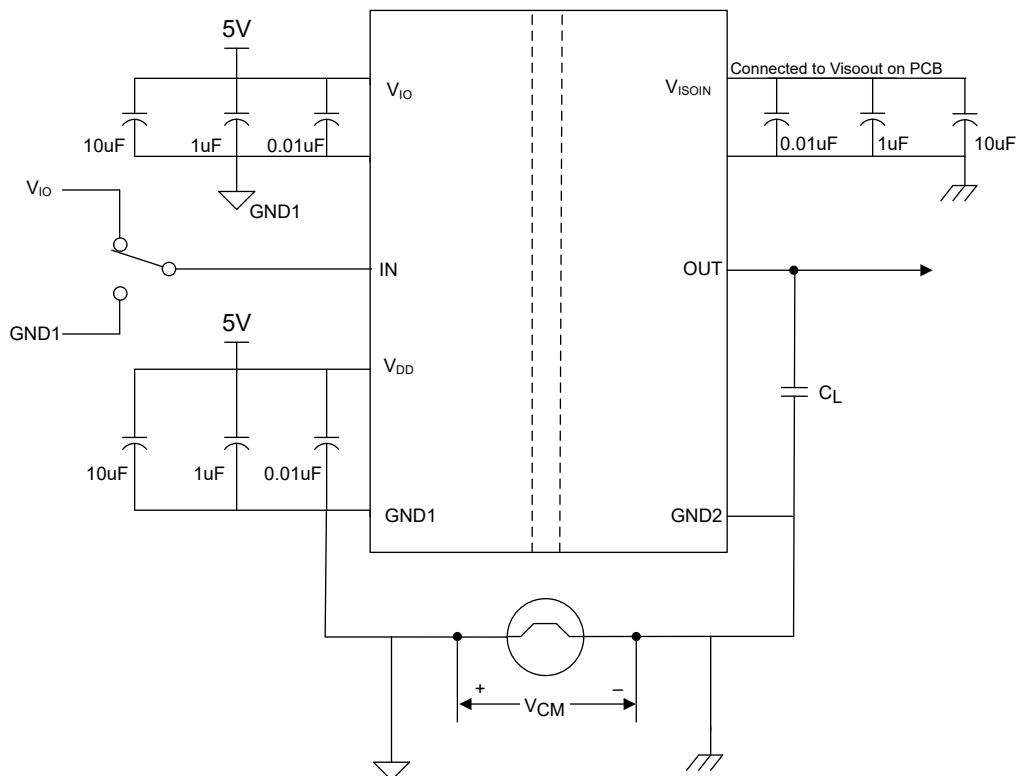
Note

A. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Note

B. Power Supply Ramp Rate = 10 mV/ns.

Figure 8-3. Default Output Delay Time Test Circuit and Voltage Waveforms



Note

$C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Note

Pass-fail criteria: Outputs must remain stable.

Figure 8-4. Common-Mode Transient Immunity Test Circuit

9 Detailed Description

9.1 Overview

The ISOW774x family of devices have low-noise, low-emissions isolated DC-DC converter, and four high-speed isolated data channels. [セクション 9.2](#) shows the functional block diagram of the ISOW774x device.

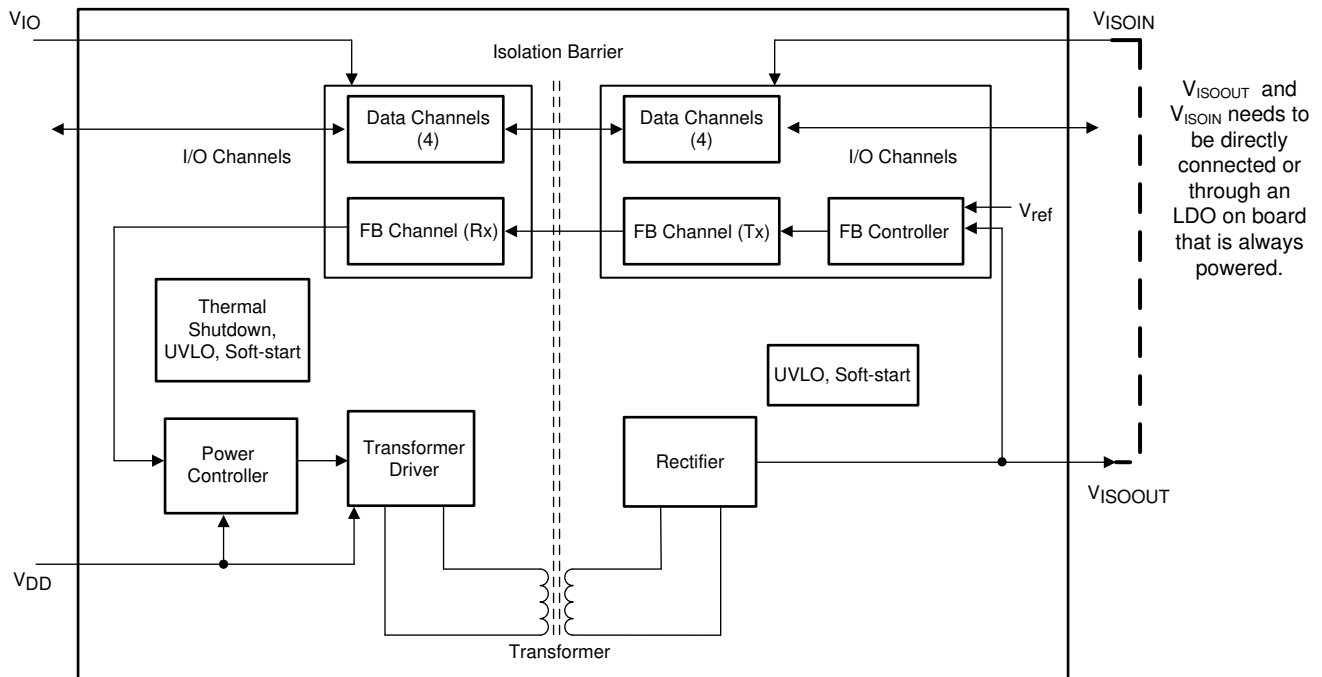
9.1.1 Power Isolation

The integrated isolated DC-DC converter uses advanced circuit and on-chip layout techniques to reduce radiated emissions and achieve upto 46% typical efficiency. The integrated transformer uses thin film polymer as the insulation barrier. Output voltage of power converter can be controlled to 3.3 V or 5 V using V_{SEL} pin. The DC-DC converter can be switched off using the EN/FLT pin to save power. The output voltage, V_{ISOOUT} , is monitored and feedback information is conveyed to the primary side through a dedicated isolation channel. V_{ISOOUT} needs to be connected to V_{ISOIN} to ensure the feedback channel is properly powered to regulate the DC-DC converter. This can be achieved by connecting the pins directly or through an LDO that remains powered up at all times. A ferrite bead is recommended between V_{ISOOUT} and V_{ISOIN} to further reduce emissions. See the [セクション 10.2](#) section. The duty cycle of the primary switching stage is adjusted accordingly. The fast feedback control loop of the power converter ensures low overshoots and undershoots during load transients. Undervoltage lockout (UVLO) with hysteresis is integrated on the V_{IO} , V_{DD} and V_{ISOIN} supplies which ensures robust fails-safe system performance under noisy conditions. An integrated soft-start mechanism ensures controlled inrush current and avoids any overshoot on the output during power up.

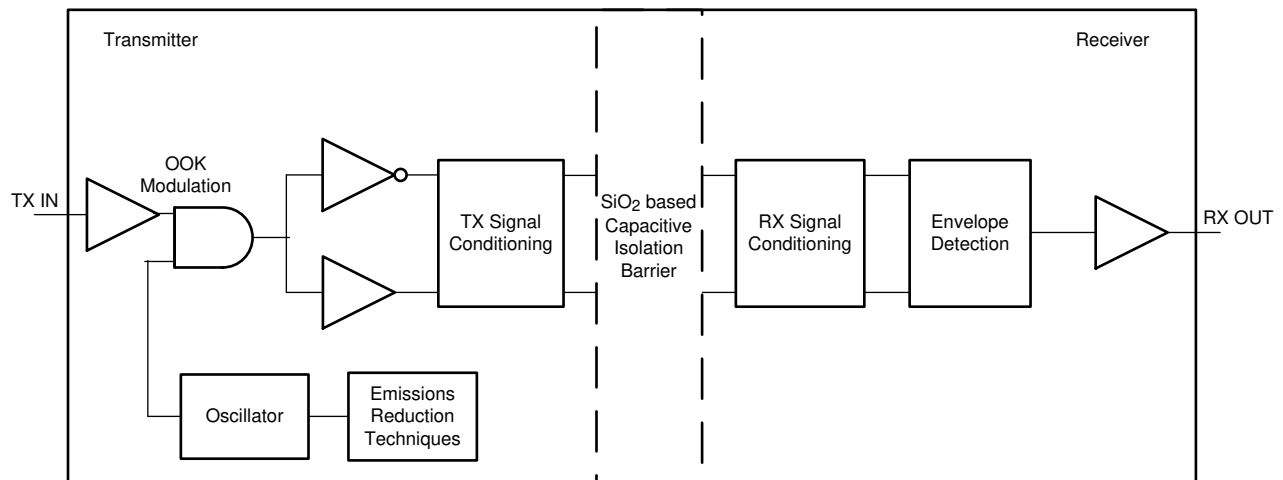
9.1.2 Signal Isolation

The integrated signal isolation channels employ an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon-dioxide based isolation barrier. The transmitter sends a high frequency carrier across the barrier to represent one state and sends no signal to represent the other state. The receiver demodulates the signal after signal conditioning and produces the output through a buffer stage. The signal-isolation channels incorporate advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions from the high frequency carrier and IO buffer switching. [図 9-1](#) shows a functional block diagram of a typical signal isolation channel. In order to keep any noise coupling from power converter away from signal path, power supplies on side 1 for power converter (V_{DD}) and signal path (V_{IO}) are kept separate. Similarly on side 2, power converter output (V_{ISOOUT}) needs to be connected to V_{ISOIN} externally on PCB. Emissions can be further improved by placing a ferrite bead between V_{ISOOUT} and V_{ISOIN} as well as between the GND2 pins. For more details, refer to the [Layout Guidelines](#) section.

9.2 Functional Block Diagram

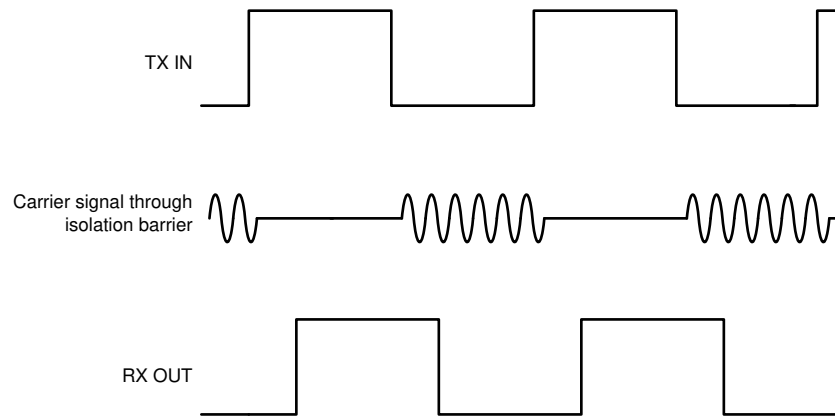


9-1. Block Diagram



9-2. Conceptual Block Diagram of a Capacitive Data Channel

☒ 9-3 shows a conceptual detail of how the OOK scheme works.



☒ 9-3. On-Off Keying (OOK) Based Modulation Scheme

9.3 Feature Description

表 9-1 shows an overview of the device features.

表 9-1. Device Features

PART NUMBER ¹	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT STATE	RATED ISOLATION ²
ISOW7740	4 forward, 0 reverse	100 Mbps	High	5 kV _{RMS} / 7071 V _{PK}
ISOW7740F			Low	
ISOW7741	High			
ISOW7741F	Low			
ISOW7742	High			
ISOW7742F	Low			
ISOW7743	High			
ISOW7743F	Low			
ISOW7744	High			
ISOW7744F	Low			

1. The F suffix is part of the orderable part number. See the セクション 14 section for the full orderable part number.
2. For detailed isolation ratings, see the セクション 7.7 table.

9.3.1 Electromagnetic Compatibility (EMC) Considerations

The ISOW774x devices use emissions reduction schemes for the internal oscillator and advanced internal layout scheme to minimize radiated emissions at the system level.

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 32. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISOW774x devices incorporate many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.

- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.
- Power path and signal path separated to minimize internal high frequency coupling and allowing for an external filtering knob using ferrite beads available to further reduce emissions
- Reduced power converter switching frequency to 25 Mhz to reduce strength of high frequency components in emissions spectrum

9.3.2 Power-Up and Power-Down Behavior

The ISOW774x device has built-in UVLO on the V_{IO} , V_{DD} , and V_{ISOIN} supplies with positive-going and negative-going thresholds and hysteresis. Both the power converter supply (V_{DD}) and logic supply (V_{IO}) need to be present for the device to work. If either of them is below its UVLO, both the signal path and the power converter are disabled.

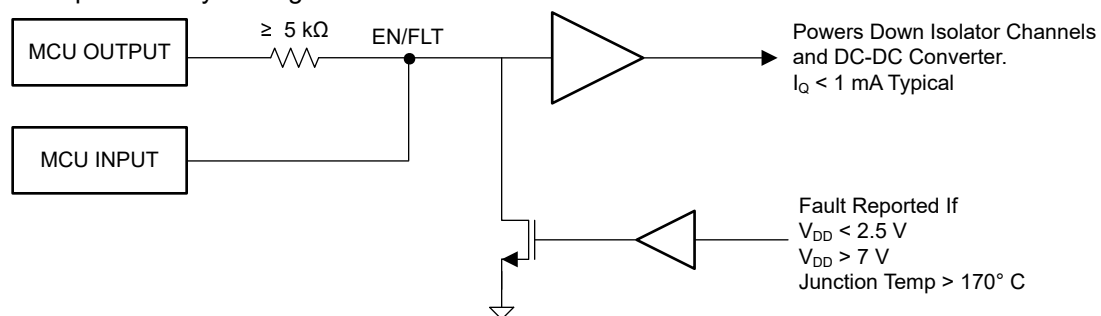
When the V_{DD} voltage crosses the positive-going UVLO threshold during power-up, the DC-DC converter initializes and the power converter duty cycle is increased in a controlled manner. This soft-start scheme limits primary peak currents drawn from the V_{DD} supply and charges the V_{ISOOUT} output in a controlled manner, avoiding overshoots. Outputs of the isolated data channels are in an indeterminate state until the V_{IO} or V_{DD} voltage crosses the positive-going UVLO threshold. When the UVLO positive-going threshold is crossed on the secondary side V_{ISOOUT} pin, the feedback data channel starts providing feedback to the primary controller. The regulation loop takes over and the isolated data channels go to the normal state defined by the respective input channels or their default states. Design should consider a sufficient time margin (typically 10 ms with 10- μ F load capacitance) to allow this power up sequence before valid data channels are accounted for system functionality.

When either V_{IO} or V_{DD} power is lost, the primary side DC-DC controller turns off when the UVLO lower threshold is reached. The V_{ISOOUT} capacitor then discharges depending on the external load. The isolated data outputs on the V_{ISOIN} side are returned to the default state for the brief time that the V_{ISOIN} voltage takes to discharge to zero.

9.3.3 Protection Features

The ISOW774x devices have multiple protection features to create a robust system level solution.

- The Enable DC-DC / FAULT protection feature (EN/FLT) can be used as either an input pin, to enable or disable the integrated DC-DC power converter, or as an output pin, which works as an alert signal if the power converter is not operating properly. In the /FAULT use case, an alert is reported if $V_{DD} > 7$ V, $V_{DD} < 2.5$ V, or if the junction temperature $> 170^{\circ}\text{C}$. When a fault is detected, this pin will go low, disabling the DC-DC converter to prevent any damage.



9-4. EN/FLT Fault Pin Diagram

- An over-voltage clamp feature is present on V_{ISOOUT} which will clamp the voltage at 6 V, when $V_{SEL} = V_{ISOOUT}$, or 4 V, when $V_{SEL} = \text{GND2}$, if there is an increase in voltage seen on V_{ISOOUT} . It is recommended that the V_{ISOOUT} stays lower than the over-clamp voltage for device reliability.
- Over-voltage lock out on V_{DD} will occur when a voltage higher than 7 V is seen. The device will go into a low power state and the EN/FLT pin will go low.

- The device is protected against output overload and short circuit. Output voltage starts dropping when the power converter is not able to deliver the current demanded during overload conditions. For a V_{ISOOUT} short-circuit to ground, the duty cycle of the converter is limited to help protect against any damage.
- The device is protected against output overload and short circuit. Output voltage starts dropping when the power converter is not able to deliver the current demanded during overload conditions. For a V_{ISOOUT} short-circuit to ground, the duty cycle of the converter is limited to help protect against any damage.
- The device is protected against output overload and short circuit. Output voltage starts dropping when the power converter is not able to deliver the current demanded during overload conditions. For a V_{ISOOUT} short-circuit to ground, the duty cycle of the converter is limited to help protect against any damage.
- Thermal protection is also integrated to help prevent the device from getting damaged during overload and short-circuit conditions on the isolated output. Under these conditions, the device temperature starts to increase. When the temperature goes above 165°C, thermal shutdown activates and the primary controller turns off which removes the energy supplied to the V_{ISOOUT} load, which causes the device to cool off. When the junction temperature goes below 150°C, the device starts to function normally. If an overload or output short-circuit condition prevails, this protection cycle is repeated. Care should be taken in the design to prevent the device junction temperatures from reaching such high values.

9.4 Device Functional Modes

表 9-2 lists the supply configurations for these devices.

表 9-2. Supply Configuration Function Table

$V_{DD}^{(1)}$	V_{IO}	VSEL	$V_{ISOOUT}^{(2)}$
$< V_{DD(UVLO+)}$	$> V_{IO(UVLO+)}$	X	OFF
$> V_{DD(UVLO+)}$	$< V_{IO(UVLO+)}$	X	OFF
5 V	1.71 V to 5.5 V	High (shorted to V_{ISOOUT})	5 V
5 V or 3.3 V	1.71 V to 5.5 V	Low (shorted to GND2) ⁽²⁾	3.3 V

- (1) $V_{DD} = 3.3$ V, MODE shorted to V_{ISOOUT} (essentially $V_{ISOOUT} = 5$ V) is not the recommended mode of operation
(2) The MODE pin has a weak pulldown internally. Therefore for $V_{ISOOUT} = 3.3$ V, the MODE pin should be strongly connected to the GND2 pin in noisy system scenarios.
(3) V_{ISOOUT} shorted to V_{ISOIN} on PCB and both GND2 pins are shorted to each other and EN=High

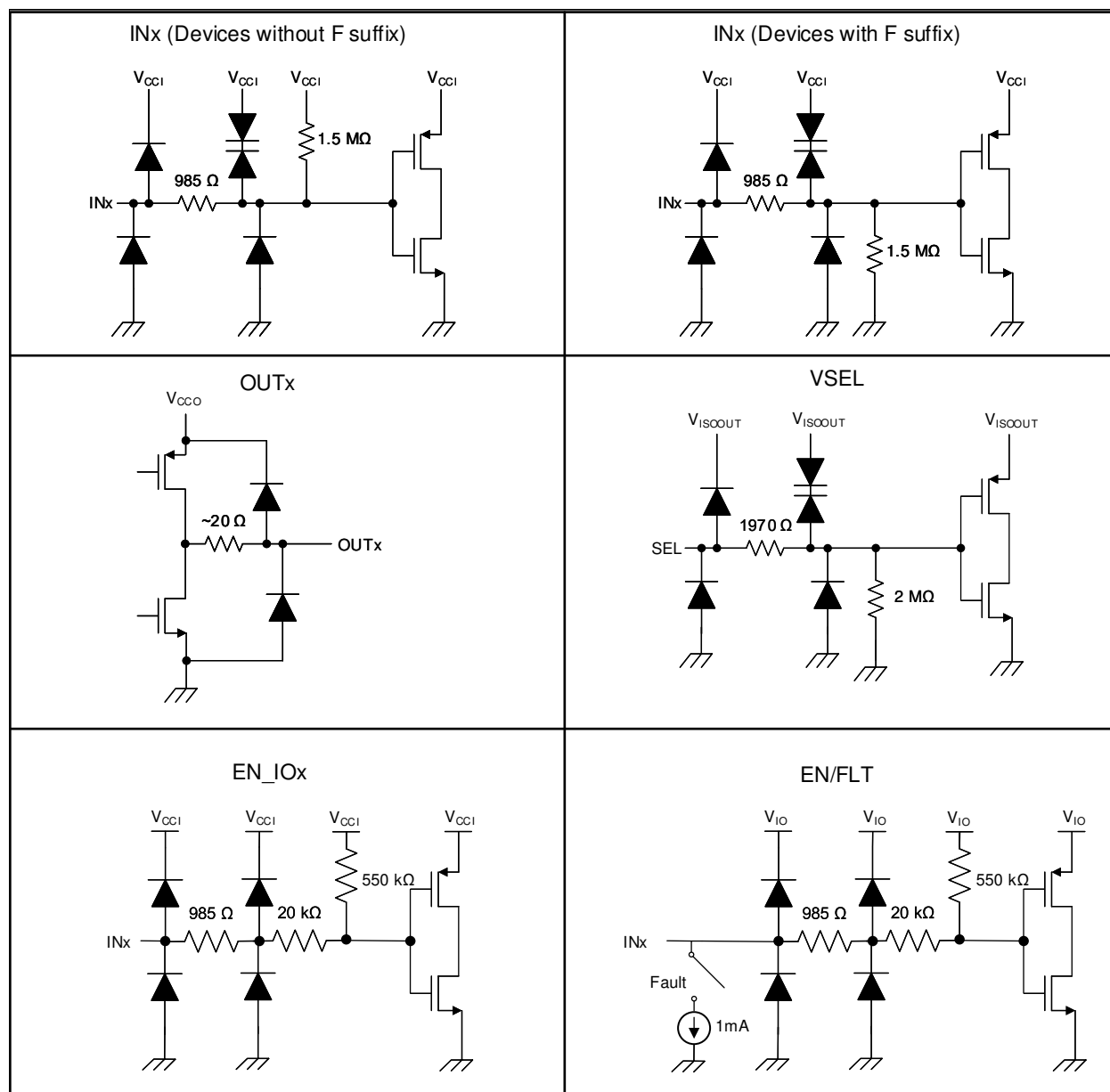
表 9-3 lists the channel isolators functional modes for these devices.

表 9-3. Channel Isolator Function Table

CHANNEL INPUT SUPPLY ($V_{CCI}^{(1)}$)	CHANNEL OUTPUT SUPPLY ($V_{CCO}^{(1)}$)	INPUT (INx)	IO ENABLE (EN_IOx)	OUTPUT (OUTx)	COMMENTS
PU	PU	H	H or Open	H	Normal Operation: A channel output assumes the logic state of its input.
		L	H or Open	L	
		Open	H or Open	Default	Default mode ⁽²⁾ : When INx is open, the corresponding channel output goes to its default logic state.
		X	L	Z and Default	A low value of output enable causes the outputs of the same side to be high impedance and the output of opposite side to be fail-safe default state.
PD	PU	X	H or Open	Default	Default mode ⁽²⁾ : When V_{CCI} is unpowered, a channel output assumes the logic state based on the selected default option. When V_{CCI} transitions from unpowered to powered-up, a channel output assumes the logic state of the input. When V_{CCI} transitions from powered-up to unpowered, channel output assumes the selected default state.

- (1) V_{CCI} = Input-side V_{IO} or V_{ISOIN} ; V_{CCO} = Output-side V_{IO} or V_{ISOIN} ; PU = Powered up ($V_{IO} > 1.7$ V, $V_{ISOIN} > 1.7$ V); PD = Powered down ($V_{IO} < 1$ V, $V_{ISOIN} < 1$ V); X = Irrelevant; H = High level; L = Low level.
(2) In the default condition, the output is high for the ISOW774x device and low with the F suffix.

9.4.1 Device I/O Schematics



 **9-5. Device I/O Schematics**

10 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The device is a high-performance, quad channel digital isolator with integrated DC-DC converter. Typically digital isolators require two power supplies isolated from each other to power up both sides of device. Due to the integrated DC-DC converter in the device, the isolated supply is generated inside the device that can be used to power isolated side of the device and peripherals on isolated side, thus saving board space. The device uses single-ended CMOS-logic switching technology. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is Microcontroller or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

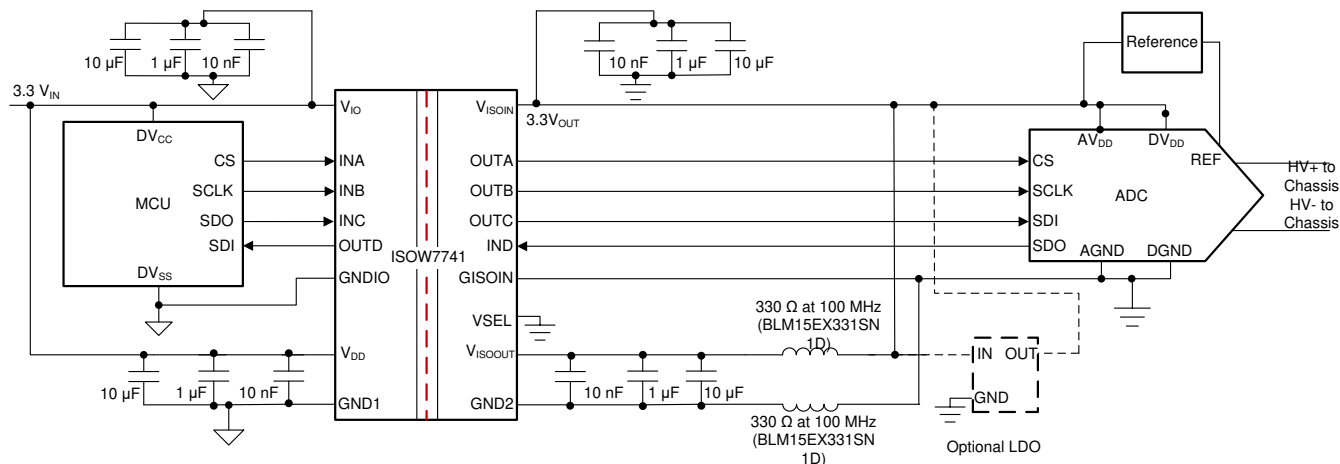
The device is suitable for applications that have limited board space and desire more integration. The device is also suitable for very high voltage applications, where power transformers meeting the required isolation specifications are bulky and expensive.

10.2 Typical Application



For step-by-step design procedure, circuit schematics, bill of materials, printed circuit board (PCB) files, simulation results, and test results, refer to [TI Design TIDA-01333, Eight-Channel, Isolated, High-Voltage Analog Input Module With ISOW7841 Reference Design](#).

10-1 shows the typical schematic for SPI isolation.



10-1. Isolated Power and SPI for ADC Sensing Application with ISOW7741

10.2.1 Design Requirements

To design with this device, use the parameters listed in [表 10-1](#).

表 10-1. Design Parameters

PARAMETER	VALUE
V_{DD} input voltage	3 V to 5.5 V
V_{IO} input voltage	1.71 V to 5.5 V
V_{ISOIN} input voltage	1.71 V to 5.5 V
V_{DD} decoupling capacitors	10 μ F + 1 μ F + 0.01 μ F + optional additional capacitance
V_{IO} decoupling capacitors	0.1 μ F + optional additional capacitance
V_{ISOIN} decoupling capacitors	0.1 μ F + optional additional capacitance
V_{ISOOUT} decoupling capacitors	10 μ F + 1 μ F + 0.01 μ F + optional additional capacitance
V_{ISOOUT} to V_{ISOIN} series inductor	BLM15ELX9331SN1D
GND2 to GISOIN series inductor	BLM15ELX9331SN1D
V_{IO} series inductor	BLM15ELX9331SN1D
V_{DD} series inductor	BLM15ELX9331SN1D
GND1 to GNDIO series inductor	BLM15ELX9331SN1D

Because of very-high current flowing through the ISOW7741 device V_{DD} and V_{ISOOUT} supplies, higher decoupling capacitors typically provide better noise and ripple performance. Although a 10- μ F capacitor is adequate, higher decoupling capacitors (such as 47 μ F) on both the V_{DD} and V_{ISOOUT} pins to the respective grounds are strongly recommended to achieve the best performance.

10.2.2 Detailed Design Procedure

The devices requires specific placement of external bypass capacitors and ferrite beads to operate at high performance. These low-ESR ceramic bypass capacitors must be placed as close to the chip pads as possible.

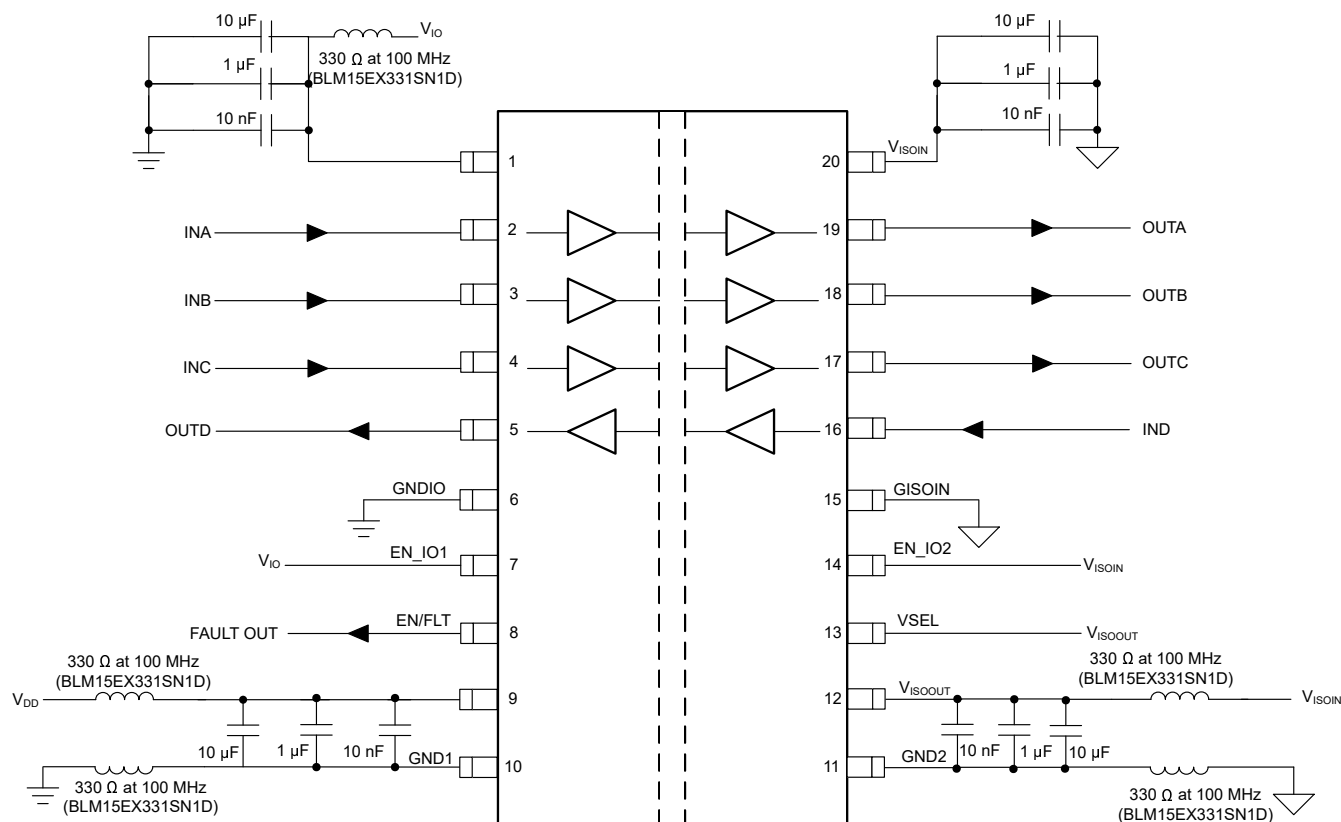
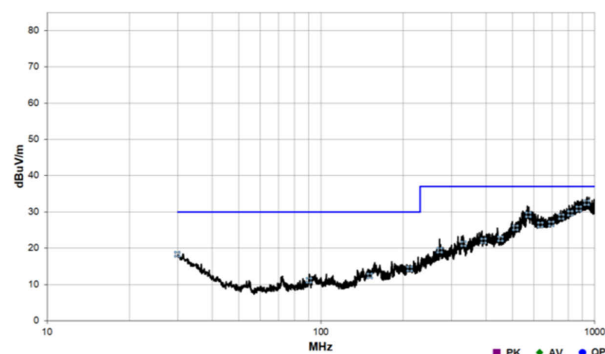


FIG 10-2. Typical ISOW7741 Circuit Hook-Up

10.2.3 Application Curve



$V_{DD} = 5\text{ V}$

$V_{ISOOUT} = 5\text{ V}$

$I_{ISOOUT} = 100\text{ mA}$

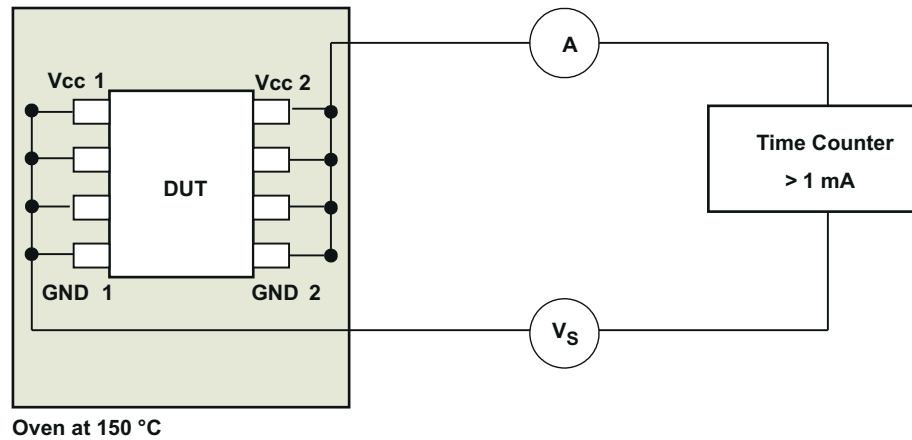
FIG 10-3. ISOW7741 Radiated Emissions versus CISPR32B line (Blue)

10.2.4 Insulation Lifetime

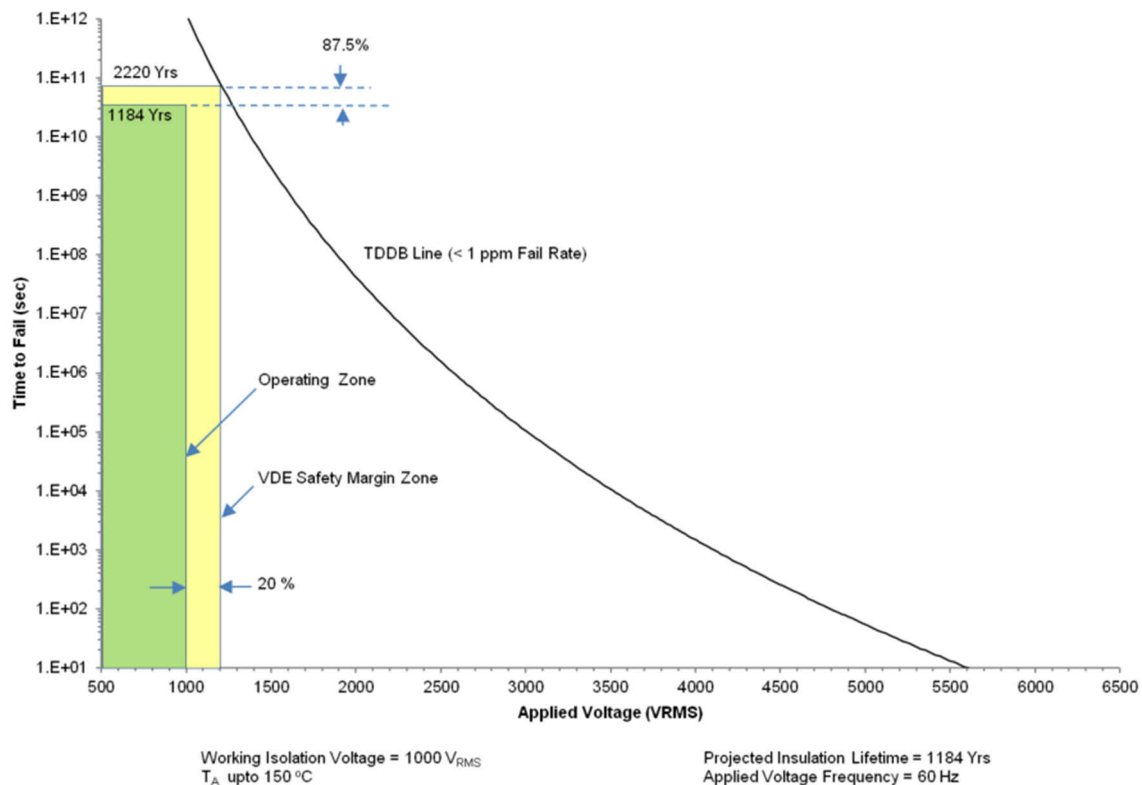
Insulation lifetime projection data is collected by using industry-standard Time Dependent Dielectric Breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together creating a two-terminal device and high voltage applied between the two sides; See FIG 10-4 for TDDB test setup. The insulation breakdown data is collected at various high voltages switching at 60 Hz over temperature. For reinforced insulation, VDE standard requires the use of TDDB projection line with failure rate of less than 1 part per million (ppm). Even though the expected minimum insulation lifetime is 20 years at the specified working isolation voltage, VDE reinforced certification requires additional safety margin of 20% for working voltage and 87.5% for

lifetime which translates into minimum required insulation lifetime of 37.5 years at a working voltage that's 20% higher than the specified value.

10-5 shows the intrinsic capability of the isolation barrier to withstand high voltage stress over its lifetime. Based on the TDDb data, the intrinsic capability of the insulation is 1000 V_{RMS} with a lifetime of 1184 years.



10-4. Test Setup for Insulation Lifetime Measurement



10-5. Insulation Lifetime Projection Data

11 Power Supply Recommendations

To help make sure that operation is reliable at data rates and supply voltages, adequate decoupling capacitors must be located as close to supply pins as possible. V_{ISOOUT} needs to be connected to V_{ISOIN} to ensure the feedback channel is properly powered to regulate the DC-DC converter. If V_{ISOOUT} and V_{ISOIN} are not connected, the DC-DC converter will run open loop and the V_{ISOOUT} voltage will drift until the over-voltage clamp clamps at 6 V. There are two ways to connect V_{ISOOUT} and V_{ISOIN} :

- 1) connect V_{ISOOUT} and V_{ISOIN} directly with a ferrite bead. A ferrite bead is recommended between V_{ISOOUT} and V_{ISOIN} to further reduce emissions.
- 2) connect V_{ISOOUT} and V_{ISOIN} with a ferrite bead through an LDO that remains powered up at all times. If the LDO has an EN pin then keep the EN high at all times.

The input supply (V_{IO} and V_{DD}) must have an appropriate current rating to support output load and switching at the maximum data rate required by the end application. For more information, refer to the [セクション 10.2](#) section.

For an output load current of 110 mA, it is recommended to have >600 mA of input current limit and for lower output load currents, the input current limit can be proportionally lower.

12 Layout

12.1 Layout Guidelines

A low cost two layer PCB should be sufficient to achieve good EMC performance:

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

Because the device has no thermal pad to dissipate heat, the device dissipates heat through the respective GND pins. Ensure that enough copper is present on both GND pins to prevent the internal junction temperature of the device from rising to unacceptable levels.

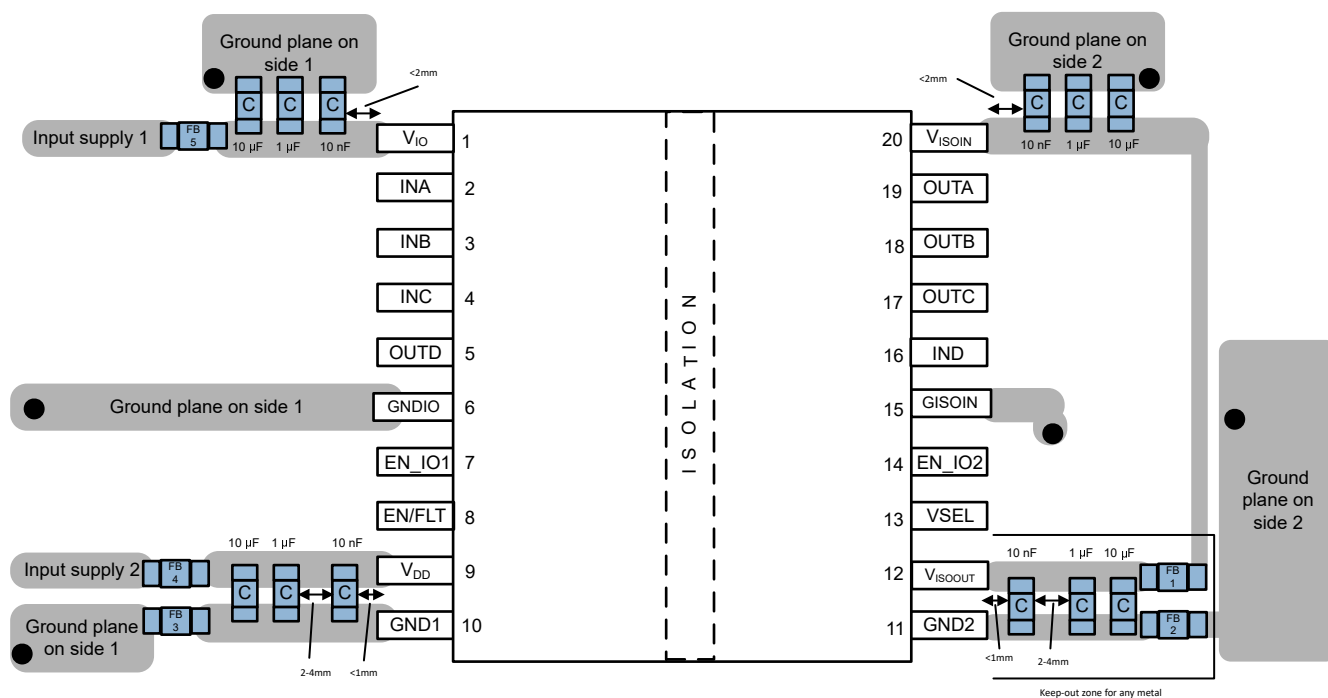
✉ 12-1 shows the recommended placement and routing of device bypass capacitors. Below guidelines must be followed to meet application EMC requirements:

- High frequency bypass capacitors 10 nF must be placed close to V_{DD} and V_{ISOOUT} pins, less than 1 mm distance away from device pins. This is very essential for optimised radiated emissions performance. Ensure that these capacitors are 0402 size so that they offer least inductance (ESL).
- Bulk capacitors of atleast 10 μ F must be placed on power converter input (V_{DD}) and output (V_{ISOOUT}) supply pins.
- Traces on V_{DD} and GND1 must be symmetric till bypass capacitors. Similarly traces on V_{ISOOUT} and GND2 must be symmetric.
- Place two 0402 size Ferrite beads (Part number: BLM15EX331SN1) on V_{ISOOUT} and GND2 path so that any high frequency noise from power converter output sees a high impedance before it goes to other components on PCB.
- Do not have any metal traces or ground pour within 4 mm of power converter output terminals V_{ISOOUT} pin12 and GND2 pin11. VSEL pin is also in V_{ISOOUT} domain and should be shorted to either pin 11 or pin 12 for output voltage selection.
- Following the layout guidelines of EVM as much as possible is highly recommended for a low radiated emissions design.

12.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps, (or rise and fall times greater than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

12.2 Layout Example



12-1. Layout Example

13 Device and Documentation Support

13.1 Device Support

13.1.1 Development Support

For development support, refer to:

- [8-ch Isolated High Voltage Analog Input Module with ISOW7841 Reference Design](#)
- [Isolated RS-485 With Integrated Signal and Power Reference Design](#)
- [Isolated RS-232 With Integrated Signal and Power Reference Design](#)

13.2 Documentation Support

13.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Digital Isolator Design Guide](#)
- Texas Instruments, [Isolation Glossary](#)

13.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

13.4 サポート・リソース

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13.5 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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13.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

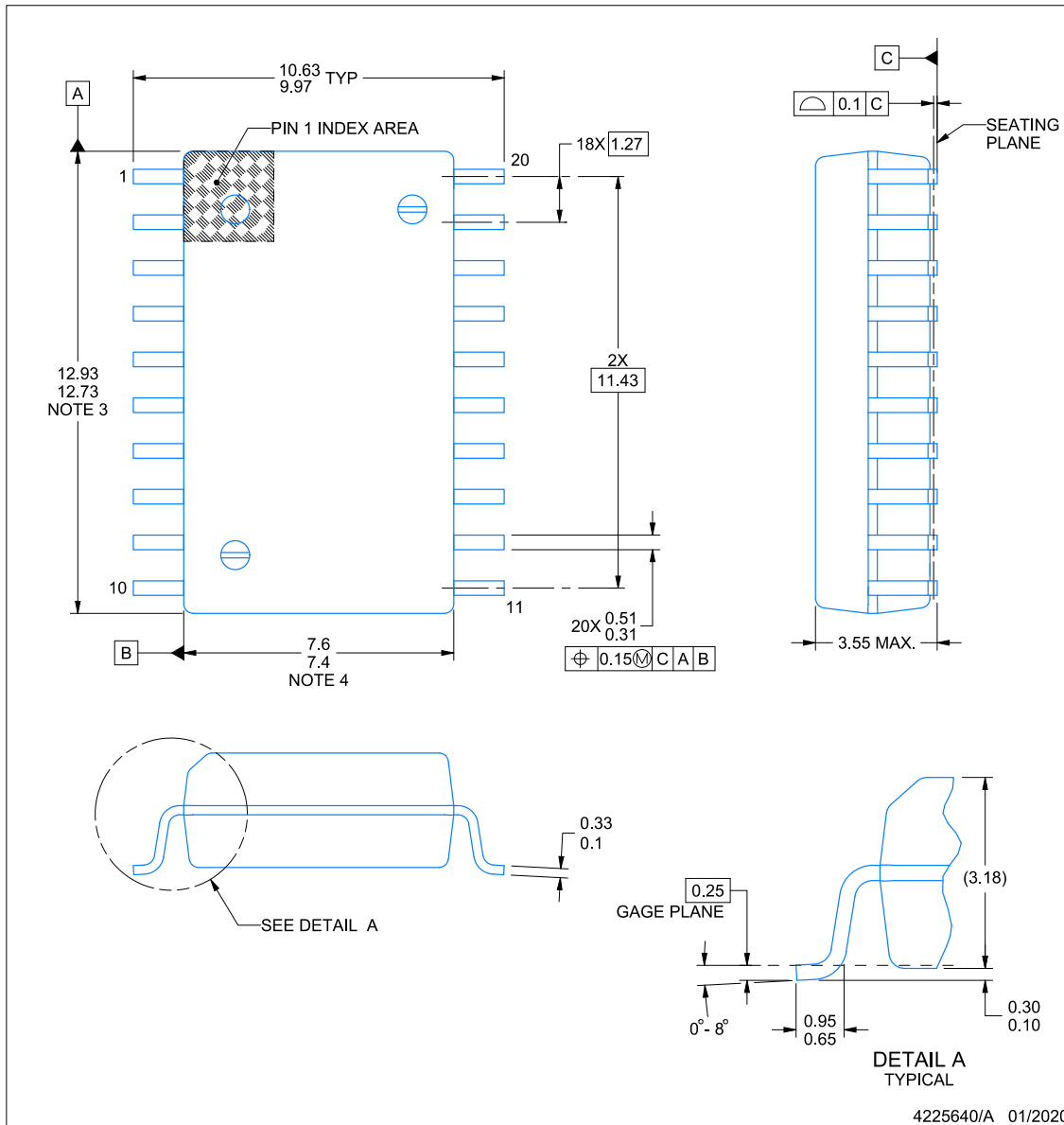
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OUTLINE

DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE

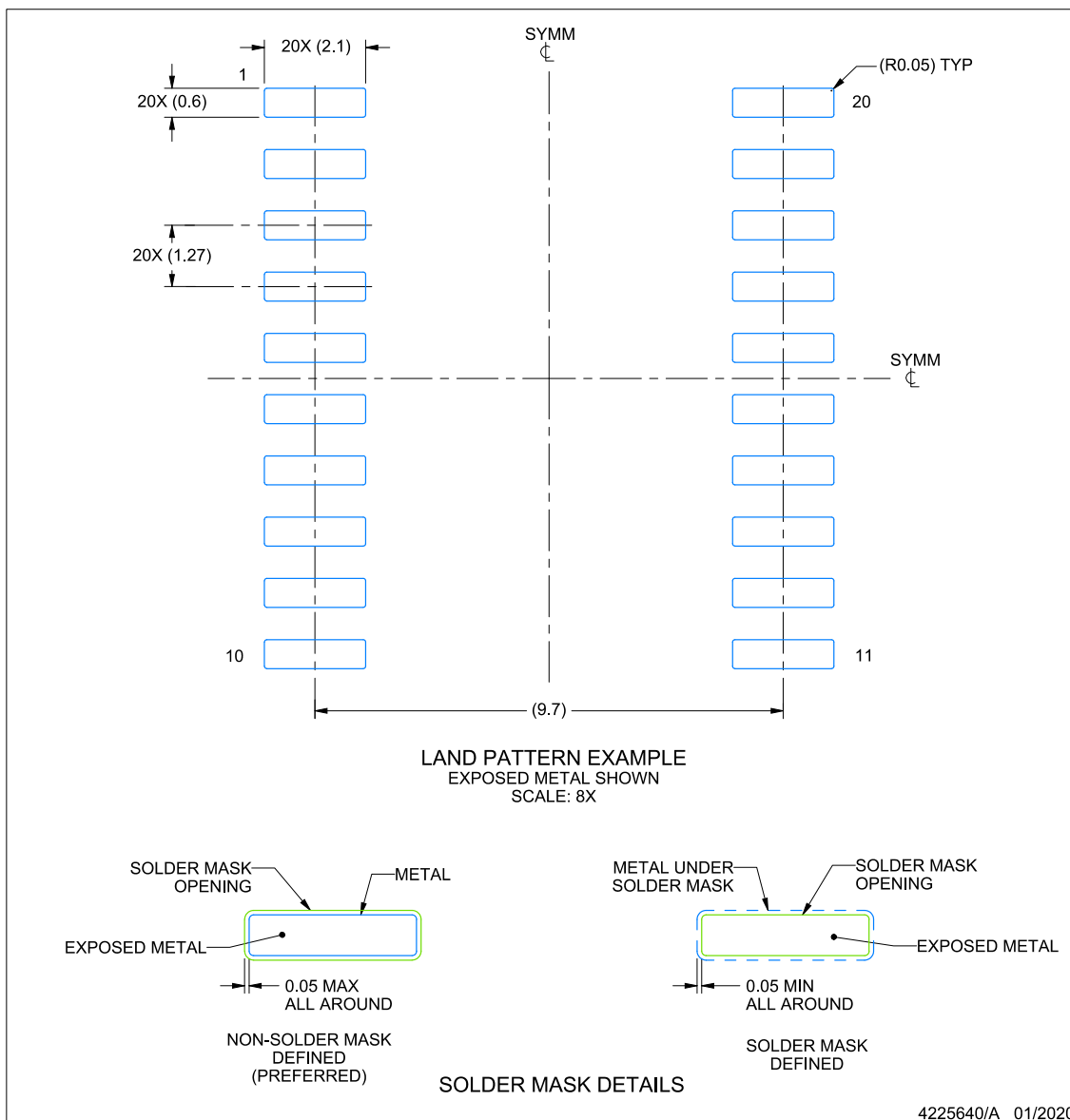


EXAMPLE BOARD LAYOUT

DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

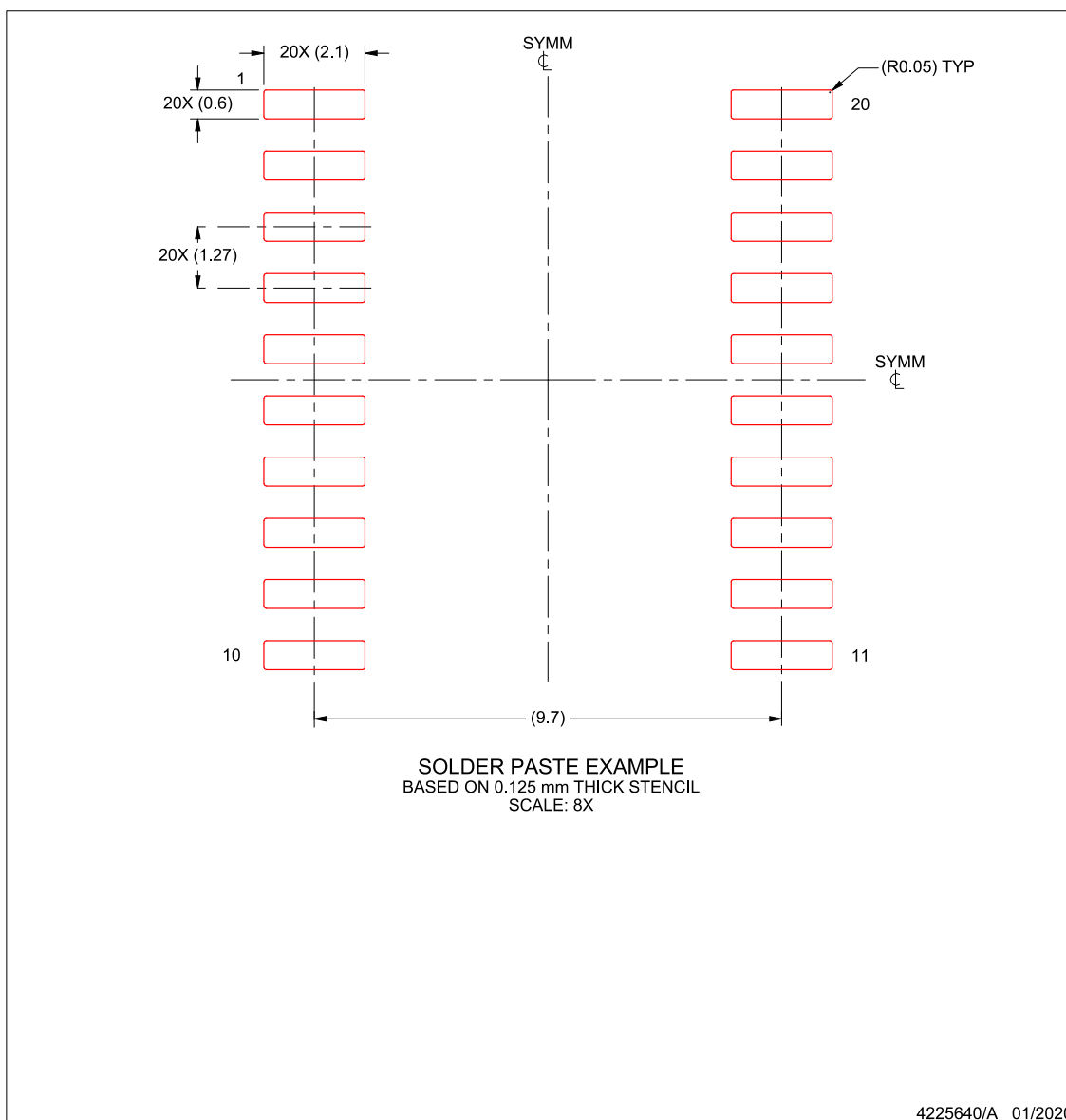
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISOW7740DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740
ISOW7740DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740
ISOW7740DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740
ISOW7740FDFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740F
ISOW7740FDFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740F
ISOW7740FDFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7740F
ISOW7741BDFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741BDFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741BDFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741
ISOW7741FBD FMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7741FBD FMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7741FBD FMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7741FDFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7741FDFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7741FDFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7741F
ISOW7742DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742
ISOW7742DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742
ISOW7742DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742
ISOW7742FDFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742F
ISOW7742FDFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742F
ISOW7742FDFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7742F
ISOW7743DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743
ISOW7743DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743
ISOW7743DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743
ISOW7743FDFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743F
ISOW7743FDFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743F

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISOW7743DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7743F
ISOW7744DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744
ISOW7744DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744
ISOW7744DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744
ISOW7744DFMR	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744F
ISOW7744DFMR.A	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744F
ISOW7744DFMR.B	Active	Production	SOIC (DFM) 20	850 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISOW7744F

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF ISOW7741, ISOW7742 :

- Automotive : [ISOW7741-Q1](#), [ISOW7742-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISOW7740DFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7740FDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7741BDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7741DFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7741FBDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7741FDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7742DFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7742FDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7743DFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7743FDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7744DFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1
ISOW7744FDFMR	SOIC	DFM	20	850	330.0	24.4	10.85	13.4	4.0	16.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

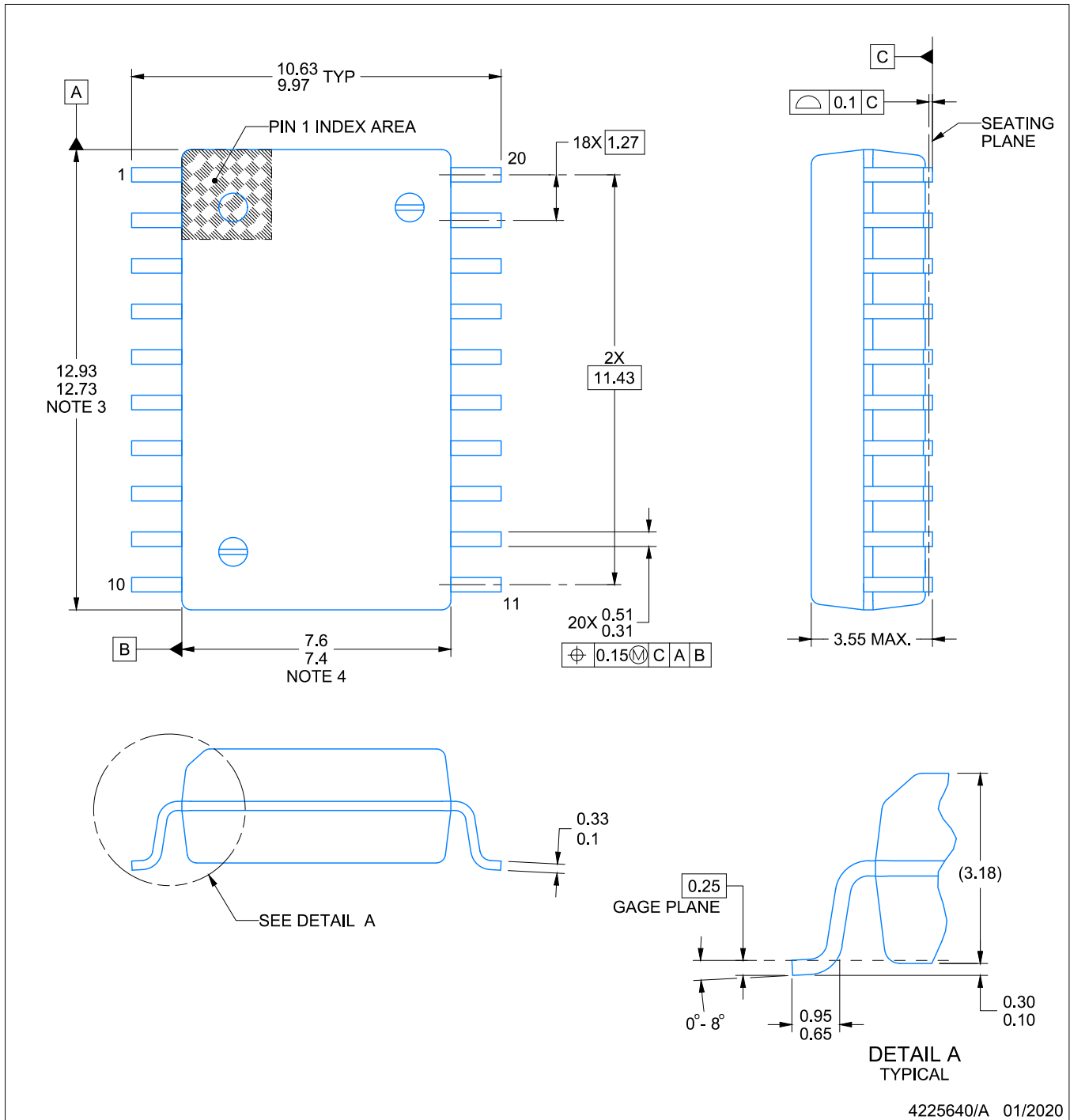
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISOW7740DFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7740FDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7741BDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7741DFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7741BDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7741FDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7742DFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7742FDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7743DFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7743FDFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7744DFMR	SOIC	DFM	20	850	350.0	350.0	43.0
ISOW7744FDFMR	SOIC	DFM	20	850	350.0	350.0	43.0

PACKAGE OUTLINE

DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE



4225640/A 01/2020

NOTES:

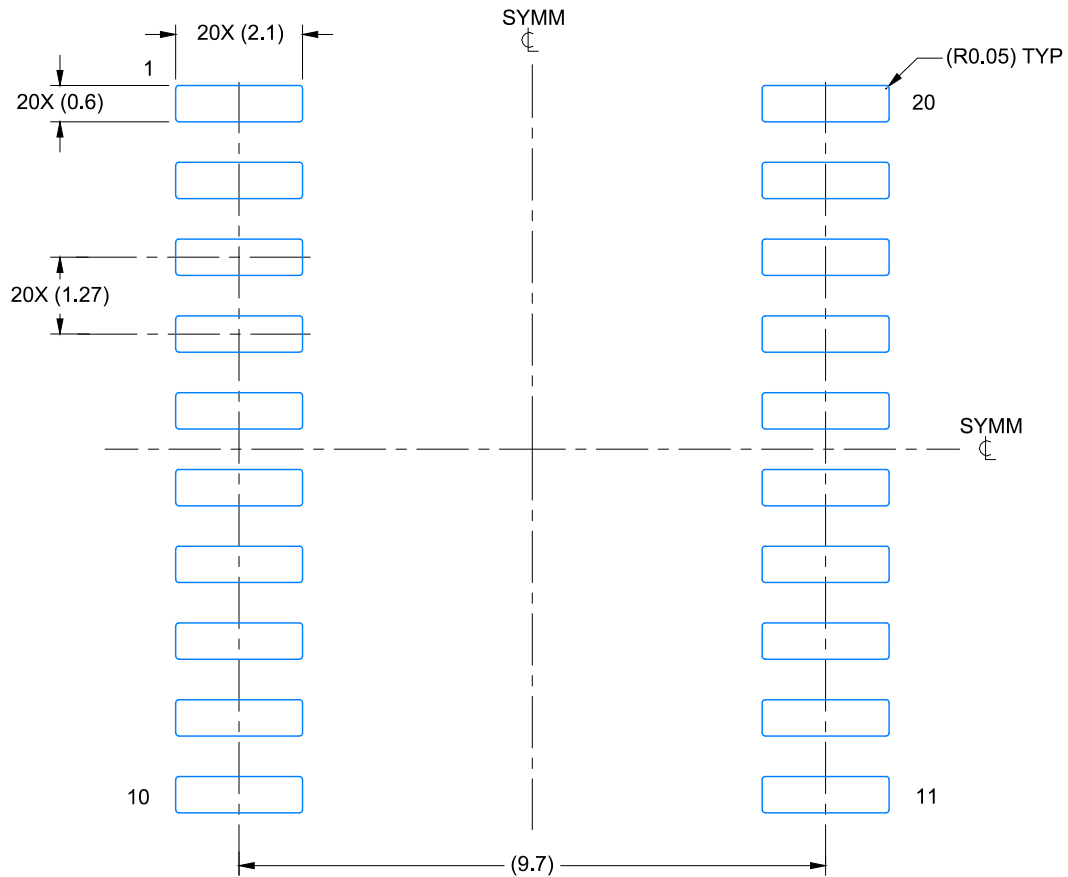
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Ref. JEDEC registration MS-013

EXAMPLE BOARD LAYOUT

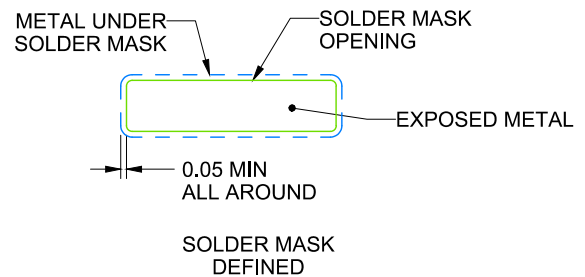
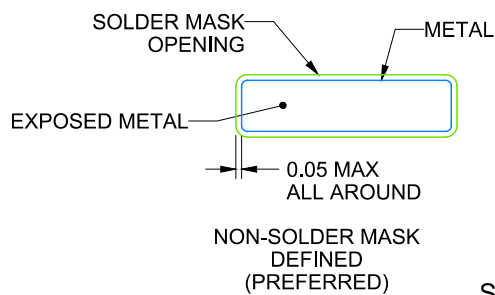
DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 8X



SOLDER MASK DETAILS

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NOTES: (continued)

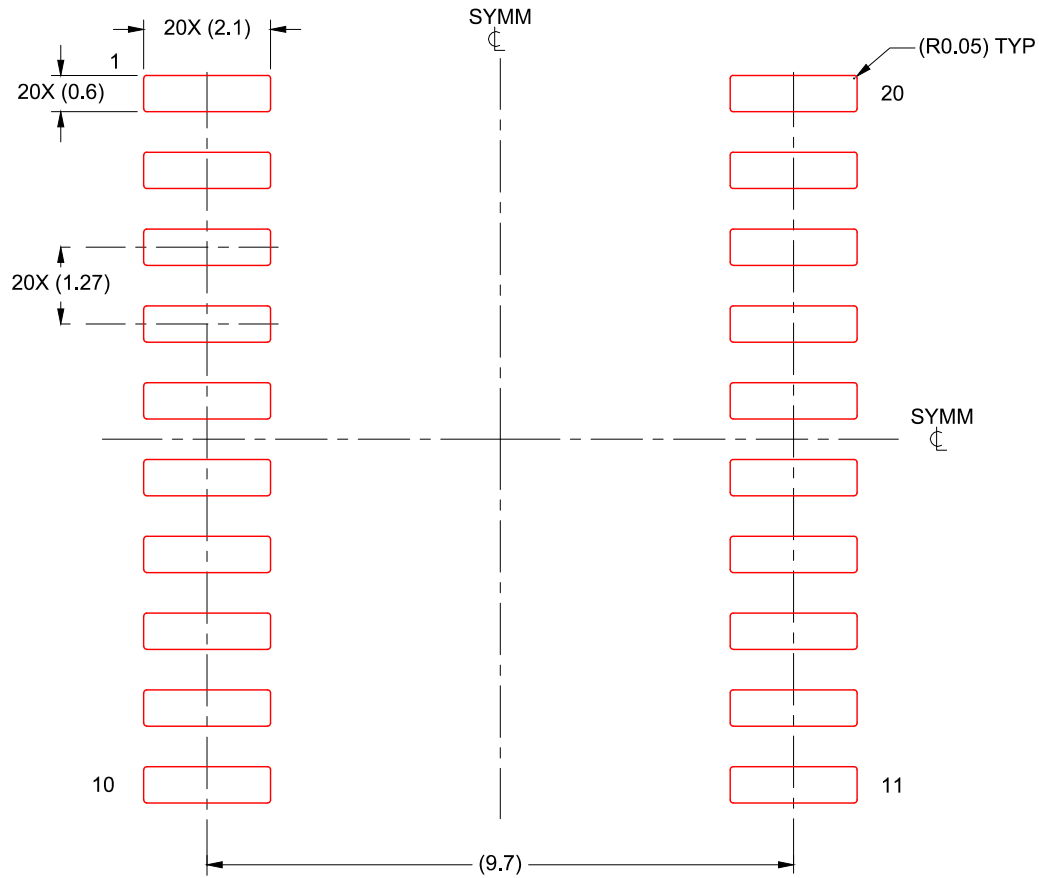
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DFM0020A

SOIC - 3.55 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 8X

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NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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